NEC Electronics Inc.

μPD421x180/L, 42S1x180/L (x = 6, 7, 8) 1,048,576 x 18-Bit Dynamic CMOS RAM

Description

The devices listed below are fast-page dynamic RAMs organized as 1M words by 18 bits and designed to operate from a single power supply. Optional features are power supply voltage (+5 V or +3.3 V), a new refresh mode called "self-refresh," and the number of cycles in a refresh period.

μPD	Power	Self-Refresh	Refresh Cycles
4216180	+5 V	—	4096 in 64 ms
180L	+3.3 V	—	
42S16180	+5 V	√	4096 in 256 ms
180L	+3.3 V	√	
4217180	+5 V	—	2048 in 32 ms
180L	+3.3 V	—	
42S17180	+5 V	√	2048 in 256 ms
180L	+3.3 V	√	
4218180	+5 V	—	1024 in 16 ms
180L	+3.3 V	—	
42S18180	+5 V	√	1024 in 256 ms
180L	+3.3 V	√	

Note: Letters L and S denote 3.3-volt and self-refresh devices, respectively.

Advanced polycide technology using stacked capacitors minimizes silicon area and provides high storage cell capacity, high performance, and high reliability. A single-transistor dynamic storage cell and CMOS circuitry throughout ensure minimum power dissipation while an on-chip circuit internally generates the negative voltage substrate bias—automatically and transparently.

The three-state I/O pins are controlled by $\overline{UCAS}$ and $\overline{LCAS}$ independent of $\overline{RAS}$. After a valid read or read-modify-write cycle, upper or lower byte data is held on the outputs by maintaining $\overline{UCAS}$ or $\overline{LCAS}$ low. Data outputs return to high impedance when $\overline{UCAS}$ or $\overline{LCAS}$ goes high. Fast-page read and write cycles can be executed by cycling $\overline{UCAS}$ or $\overline{LCAS}$.

Refreshing may be accomplished by a $\overline{CAS}$ before $\overline{RAS}$ refresh cycle (CBR) that internally generates the refresh addresses.

For the 4216/42S16, $\overline{RAS}$ only refresh cycles and normal read or write cycles on the 4096 address combinations of A_0 - A_{11} will refresh all memory locations. Bits A_0 - A_{11} are used for row and refresh addresses, A_0 - A_7 for column addresses.

For the 4217/42S17, $\overline{RAS}$ only refresh cycles and normal read or write cycles on the 2048 address combinations of A_0 - A_{10} will refresh all memory locations. Bits A_0 - A_{10} are used for row and refresh addresses, A_0 - A_8 for column addresses.

For the 4218/42S18, $\overline{RAS}$ only refresh cycles and normal read or write cycles on the 1024 address combinations of A_0 - A_9 will refresh all memory locations. Bits A_0 - A_9 are used for row, refresh, and column addresses.

The self-refresh mode is entered by holding $\overline{RAS}$ and $\overline{CAS}$ low for longer than 100 μs during a CBR cycle. Detection of this long $\overline{RAS}$ time starts an internal oscillator that maintains data integrity without external clocking. The slow refresh reduces the data hold current to less than 200 μA (+5 V) or 80 μA (+3.3 V). Self-refresh mode is used with microprocessors that have a "sleep mode" for low-power applications such as notebook PCs.

Battery backup current I_{CC6} is defined as the current consumption when the device is in standby mode ($\overline{RAS} \geq V_{CC} - 0.2$ V) and very-slow (extended) CBR cycles are being performed.

Features

- 1,048,576 by 18-bit organization
- Single power supply: +5-volt or +3.3 volt
- Fast-page option
- Low-power operation
- Byte read/write control with $\overline{UCAS}$ and $\overline{LCAS}$
- $\overline{CAS}$ before $\overline{RAS}$ refreshing
- Self-refresh option (slow internal automatic refresh)
- On-chip substrate bias generator
- TTL-compatible inputs and outputs
- Nonlatched three-state outputs
- Low input capacitance
- Multiplexed row and column addresses
- 42-pin SOJ and 50/44-pin TSOP plastic packages

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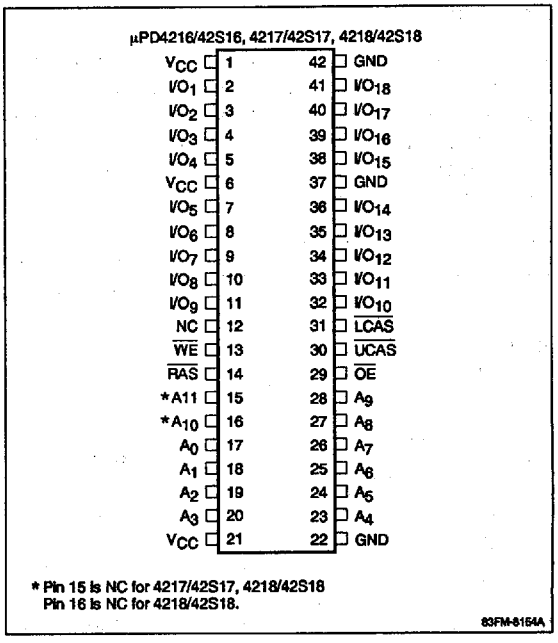
Pin Identification

Name	Function
A_0 - A_{11}	Address inputs
I/O_1 - I/O_{18}	Data inputs and outputs
$\overline{LCAS}$, $\overline{UCAS}$	Column address strobes
$\overline{OE}$	Output enable
$\overline{RAS}$	Row address strobe
$\overline{WE}$	Write enable
GND	Ground
V_{CC}	+5-volt or +3.3-volt power supply
NC	No connection

Pin Configurations

42-Pin Plastic SOJ



* Pin 15 is NC for 4217/42S17, 4218/42S18
Pin 16 is NC for 4218/42S18.

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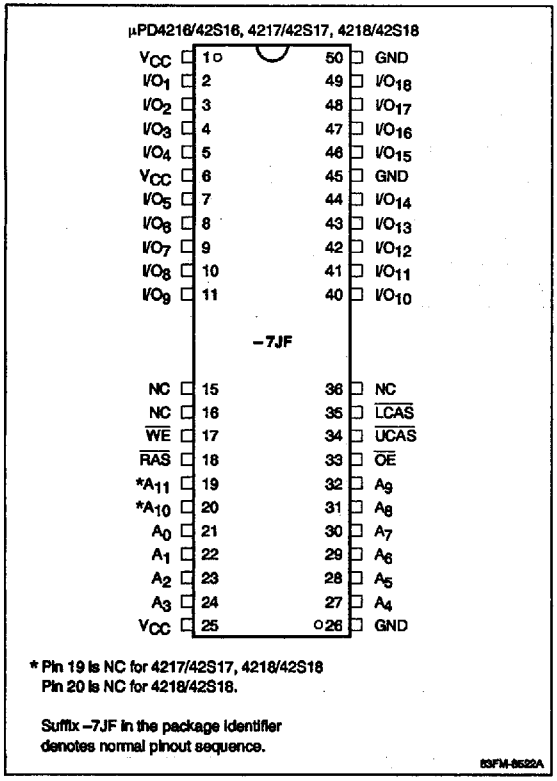
Pin Configurations (cont)

50/44-Pin Plastic TSOP (Normal Pinouts)



* Pin 19 is NC for 4217/42S17, 4218/42S18
Pin 20 is NC for 4218/42S18.

Suffix –7JF in the package identifier denotes normal pinout sequence.

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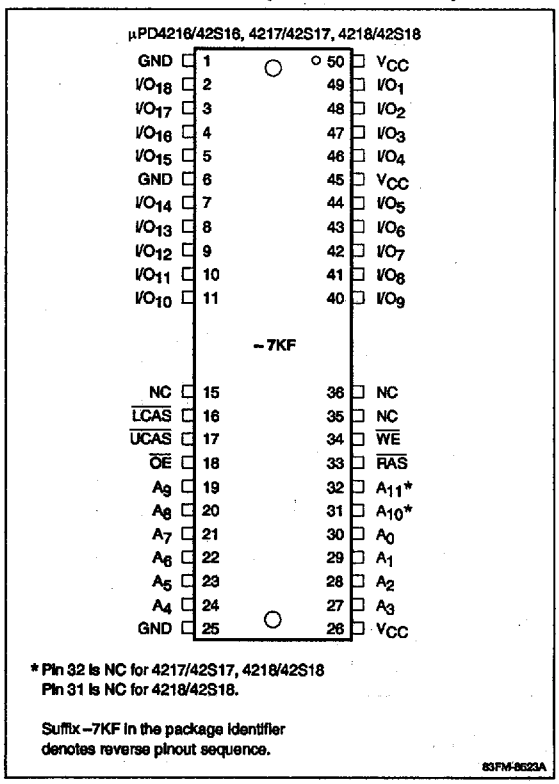
50/44-Pin Plastic TSOP (Reverse Pinouts)



* Pin 32 is NC for 4217/42S17, 4218/42S18
Pin 31 is NC for 4218/42S18.

Suffix –7KF in the package identifier denotes reverse pinout sequence.

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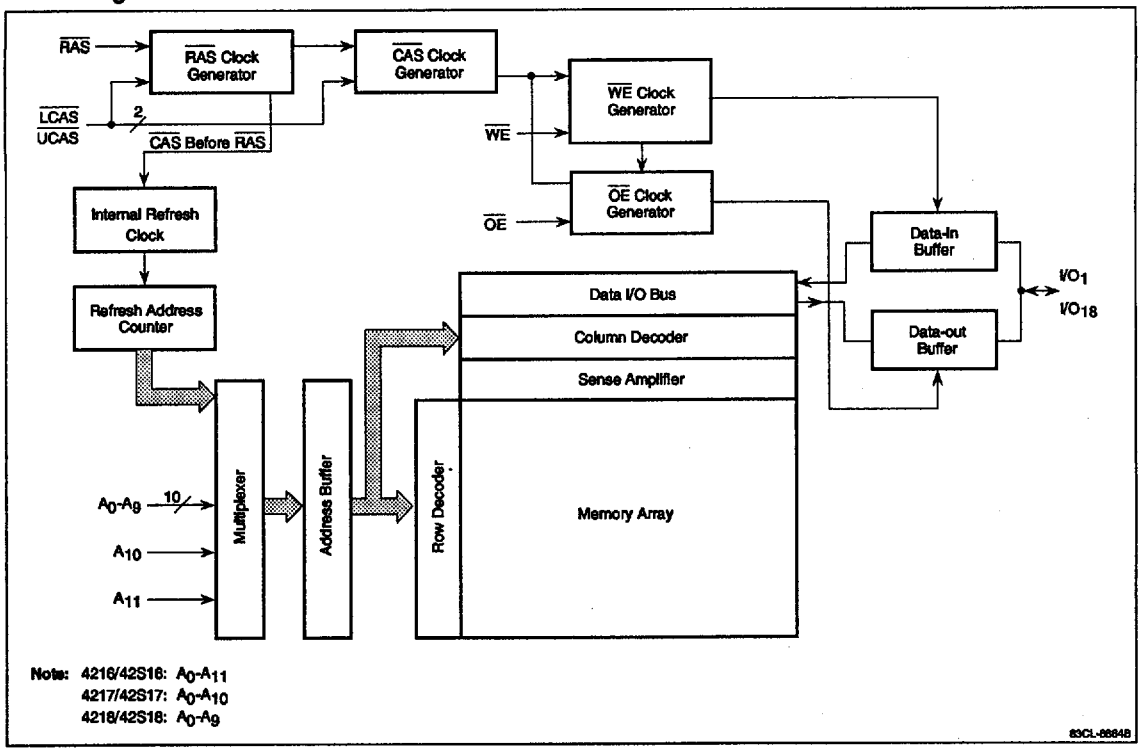
Block Diagram



Truth Table

Function	RAS	LCAS	UCAS	WE	OE	I/O1 - I/O9	I/O10 - I/O18
Standby	H	X	X	X	X	High-Z	High-Z
Refresh cycle	L	H	H	X	X	High-Z	High-Z
Byte read cycle	L	L	H	H	L	Data output	High-Z
	L	H	L	H	L	High-Z	Data output
Word read cycle	L	L	L	H	L	Data output	Data output
Byte write cycle	L	L	H	L	H	Data input	—
	L	H	L	L	H	—	Data input
Word write cycle	L	L	L	L	H	Data input	Data input
——	L	L	L	H	H	High-Z	High-Z

X = don't care.

Ordering Information, μPD4216180 (+ 5-volt power; 4096 refresh cycles)

Part Number	RAS Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD4216180LE-50	50 ns	35 ns	350 μA	42-pin plastic SOJ
LE-60	60 ns	40 ns		
LE-70	70 ns	45 ns		
LE-80	80 ns	50 ns		
μPD4216180G5-50	50 ns	35 ns	350 μA	50/44-pin plastic TSOP (normal pinouts)
G5-60	60 ns	40 ns		
G5-70	70 ns	45 ns		
G5-80	80 ns	50 ns		
μPD4216180G5M-50	50 ns	35 ns	350 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-60	60 ns	40 ns		
G5M-70	70 ns	45 ns		
G5M-80	80 ns	50 ns		

Ordering Information, μPD4216180L (+ 3.3-volt power; 4096 refresh cycles)

Part Number	RAS Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD4216180LLE-A60	60 ns	40 ns	140 μA	42-pin plastic SOJ
LE-A70	70 ns	45 ns		
LE-A80	80 ns	50 ns		
μPD4216180LG5-A60	60 ns	40 ns	140 μA	50/44-pin plastic TSOP (normal pinouts)
G5-A70	70 ns	45 ns		
G5-A80	80 ns	50 ns		
μPD4216180LG5M-A60	60 ns	40 ns	140 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-A70	70 ns	45 ns		
G5M-A80	80 ns	50 ns		

Ordering Information, μPD42S16180 (+5-volt power; 4096 refresh cycles; self-refresh mode)

Part Number	RAS Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD42S16180LE-50	50 ns	35 ns	350 μA	42-pin plastic SOJ
LE-60	60 ns	40 ns		
LE-70	70 ns	45 ns		
LE-80	80 ns	50 ns		
μPD42S16180G5-50	50 ns	35 ns	350 μA	50/44-pin plastic TSOP (normal pinouts)
G5-60	60 ns	40 ns		
G5-70	70 ns	45 ns		
G5-80	80 ns	50 ns		
μPD42S16180G5M-50	50 ns	35 ns	350 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-60	60 ns	40 ns		
G5M-70	70 ns	45 ns		
G5M-80	80 ns	50 ns		

Ordering Information, μPD42S16180L (+3.3-volt power; 4096 refresh cycles; self-refresh mode)

Part Number	RAS Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD42S16180LLE-A60	60 ns	40 ns	140 μA	42-pin plastic SOJ
LE-A70	70 ns	45 ns		
LE-A80	80 ns	50 ns		
μPD42S16180LG5-A60	60 ns	40 ns	140 μA	50/44-pin plastic TSOP (normal pinouts)
G5-A70	70 ns	45 ns		
G5-A80	80 ns	50 ns		
μPD42S16180LG5M-A60	60 ns	40 ns	140 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-A70	70 ns	45 ns		
G5M-A80	80 ns	50 ns		

Ordering Information, μPD4217180 (+ 5-volt power; 2048 refresh cycles)

Part Number	$\overline{RAS}$ Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD4217180LE-50	50 ns	35 ns	300 μA	42-pin plastic SOJ
LE-60	60 ns	40 ns		
LE-70	70 ns	45 ns		
LE-80	80 ns	50 ns		
μPD4217180G5-50	50 ns	35 ns	300 μA	50/44-pin plastic TSOP (normal pinouts)
G5-60	60 ns	40 ns		
G5-70	70 ns	45 ns		
G5-80	80 ns	50 ns		
μPD4217180G5M-50	50 ns	35 ns	300 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-60	60 ns	40 ns		
G5M-70	70 ns	45 ns		
G5M-80	80 ns	50 ns		

Ordering Information, μPD4217180L (+ 3.3-volt power; 2048 refresh cycles)

Part Number	$\overline{RAS}$ Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD4217180LLE-A60	60 ns	40 ns	120 μA	42-pin plastic SOJ
LE-A70	70 ns	45 ns		
LE-A80	80 ns	50 ns		
μPD4217180LG5-A60	60 ns	40 ns	120 μA	50/44-pin plastic TSOP (normal pinouts)
G5-A70	70 ns	45 ns		
G5-A80	80 ns	50 ns		
μPD4217180LG5M-A60	60 ns	40 ns	120 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-A70	70 ns	45 ns		
G5M-A80	80 ns	50 ns		

Ordering Information, μPD42S17180 (+ 5-volt power; 2048 refresh cycles; self-refresh mode)

Part Number	$\overline{RAS}$ Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD42S17180LE-50	50 ns	35 ns	300 μA	42-pin plastic SOJ
LE-60	60 ns	40 ns		
LE-70	70 ns	45 ns		
LE-80	80 ns	50 ns		
μPD42S17180G5-50	50 ns	35 ns	300 μA	50/44-pin plastic TSOP (normal pinouts)
G5-60	60 ns	40 ns		
G5-70	70 ns	45 ns		
G5-80	80 ns	50 ns		
μPD42S17180G5M-50	50 ns	35 ns	300 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-60	60 ns	40 ns		
G5M-70	70 ns	45 ns		
G5M-80	80 ns	50 ns		

Ordering Information, μPD42S17180L (+ 3.3-volt power; 2048 refresh cycles; self-refresh mode)

Part Number	$\overline{RAS}$ Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD42S17180LLE-A60	60 ns	40 ns	120 μA	42-pin plastic SOJ
LE-A70	70 ns	45 ns		
LE-A80	80 ns	50 ns		
μPD42S17180LG5-A60	60 ns	40 ns	120 μA	50/44-pin plastic TSOP (normal pinouts)
G5-A70	70 ns	45 ns		
G5-A80	80 ns	50 ns		
μPD42S17180LG5M-A60	60 ns	40 ns	120 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-A70	70 ns	45 ns		
G5M-A80	80 ns	50 ns		

Ordering Information, μPD4218180 (+ 5-volt power; 1024 refresh cycles)

Part Number	RAS Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD4218180LE-50	50 ns	35 ns	250 μA	42-pin plastic SOJ
LE-60	60 ns	40 ns		
LE-70	70 ns	45 ns		
LE-80	80 ns	50 ns		
μPD4218180G5-50	50 ns	35 ns	250 μA	50/44-pin plastic TSOP (normal pinouts)
G5-60	60 ns	40 ns		
G5-70	70 ns	45 ns		
G5-80	80 ns	50 ns		
μPD4218180G5M-50	50 ns	35 ns	250 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-60	60 ns	40 ns		
G5M-70	70 ns	45 ns		
G5M-80	80 ns	50 ns		

Ordering Information, μPD4218180L (+ 3.3-volt power; 1024 refresh cycles)

Part Number	RAS Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD4218180LLE-A60	60 ns	40 ns	110 μA	42-pin plastic SOJ
LE-A70	70 ns	45 ns		
LE-A80	80 ns	50 ns		
μPD4218180LG5-A60	60 ns	40 ns	110 μA	50/44-pin plastic TSOP (normal pinouts)
G5-A70	70 ns	45 ns		
G5-A80	80 ns	50 ns		
μPD4218180LG5M-A60	60 ns	40 ns	110 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-A70	70 ns	45 ns		
G5M-A80	80 ns	50 ns		

Ordering Information, μPD42S18180 (+ 5-volt power; 1024 refresh cycles; self-refresh mode)

Part Number	RAS Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD42S18180LE-50	50 ns	35 ns	250 μA	42-pin plastic SOJ
LE-60	60 ns	40 ns		
LE-70	70 ns	45 ns		
LE-80	80 ns	50 ns		
μPD42S18180G5-50	50 ns	35 ns	250 μA	50/44-pin plastic TSOP (normal pinouts)
G5-60	60 ns	40 ns		
G5-70	70 ns	45 ns		
G5-80	80 ns	50 ns		
μPD42S18180G5M-50	50 ns	35 ns	250 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-60	60 ns	40 ns		
G5M-70	70 ns	45 ns		
G5M-80	80 ns	50 ns		

Ordering Information, μPD42S18180L (+ 3.3-volt power; 1024 refresh cycles; self-refresh mode)

Part Number	RAS Access Time (max)	Fast-Page Cycle (max)	Battery Backup Current (max)	Package
μPD42S18180LLE-A60	60 ns	40 ns	110 μA	42-pin plastic SOJ
LE-A70	70 ns	45 ns		
LE-A80	80 ns	50 ns		
μPD42S18180LG5-A60	60 ns	40 ns	110 μA	50/44-pin plastic TSOP (normal pinouts)
G5-A70	70 ns	45 ns		
G5-A80	80 ns	50 ns		
μPD42S18180LG5M-A60	60 ns	40 ns	110 μA	50/44-pin plastic TSOP (reverse pinouts)
G5M-A70	70 ns	45 ns		
G5M-A80	80 ns	50 ns		

Absolute Maximum Ratings

Voltage on any pin relative to GND	
5-volt devices	−1.0 to +7.0 V
3.3-volt devices	−0.5 to + 4.6 V
Operating temperature, T_{OPR}	0 to +70°C
Storage temperature, T_{STG}	−55 to +125°C
Short-circuit output current, I_{OS}	50 mA
Power dissipation, P_D	1.0 W

Exposure to Absolute Maximum Ratings for extended periods may affect device reliability; exceeding the ratings could cause permanent damage. The device should be operated within the limits specified under DC and AC Characteristics.

Capacitance

T_A = 25°C; f = 1 MHz

Parameter	Symbol	Max	Unit	Pins Under Test
Input capacitance	C_{I1}	5	pF	Addresses
	C_{I2}	7	pF	$\overline{LCAS}$, $\overline{UCAS}$, $\overline{WE}$, $\overline{OE}$, $\overline{RAS}$
Input/output capacitance	C_O	7	pF	I/O_1 - I/O_{18}

Recommended Operating Conditions

		5-Volt Devices			3.3-Volt Devices			
Parameter	Symbol	Min	Typ	Max	Min	Typ	Max	Unit
Input voltage, high	V_{IH}	2.4		V_{CC} + 1.0	2.0		V_{CC} + 0.3	V
Input voltage, low	V_{IL}	−1.0		0.8	−0.3		0.8	V
Supply voltage	V_{CC}	4.5	5.0	5.5	3.0	3.3	3.6	V
Ambient temperature	T_A	0		70	0		70	°C

Self-Refresh Current; 42S1x Devices

T_A = 0 to +70°C; V_{CC} = +5 V ±10% or +3.3 V ±0.3 V

Symbol	5-Volt Devices	3.3-Volt Devices	Conditions
I_{CC7}	200 μA max	80 μA max	I/O pins: $V_{IH} \geq V_{CC}$ −0.2 V; $V_{IL} \leq$ 0.2 V or open. Other input pins: $V_{IH} \geq V_{CC}$ −0.2 V; $V_{IL} \leq$ 0.2 V or open; $t_{RAS} \geq$ 100 μs

DC Characteristics; 5-Volt Devices

T_A = 0 to +70°C; V_{CC} = +5.0 V ±10%

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Standby current	I_{CC2}			2.0	mA	$\overline{RAS}$ = $\overline{CAS}$ ≥ V_{IH} (min); I_O = 0 mA
				400	μA	$\overline{RAS}$ = $\overline{CAS}$ ≥ V_{CC} − 0.2 V; I_O = 0 mA
Input leakage current	$I_{I(L)}$	−10		10	μA	V_{IN} = 0 V to V_{CC}; all other pins not under test = 0 V
Output leakage current	$I_{O(L)}$	−10		10	μA	D_{OUT} disabled; V_{OUT} = 0 V to V_{CC}
Output voltage, low	V_{OL}			0.4	V	I_{OL} = 4.2 mA
Output voltage, high	V_{OH}	2.4			V	I_{OH} = −5 mA

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DC Characteristics; 3.3-Volt Devices

T_A = 0 to +70°C; V_{CC} = +3.3 V ±0.3 V

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Standby current	I_{CC2}			2.0	mA	$\overline{RAS}$ = $\overline{CAS}$ ≥ V_{IH} (min); I_O = 0 mA
				400	μA	$\overline{RAS}$ = $\overline{CAS}$ ≥ V_{CC} – 0.2 V; I_O = 0 mA
Input leakage current	$I_{I(L)}$	–10		10	μA	V_{IN} = 0 V to V_{CC}; all other pins not under test = 0 V
Output leakage current	$I_{O(L)}$	–10		10	μA	D_{OUT} disabled; V_{OUT} = 0 V to V_{CC}
Output voltage, low	V_{OL}			0.4	V	I_{OL} = 2.0 mA
Output voltage, high	V_{OH}	2.4			V	I_{OH} = –2.0 mA

DC Current Requirements; 5-Volt Devices

Parameter	Symbol	-50	-60	-70	-80	Unit	Test Conditions
Operating current	I_{CC1}						
4216/42S16		120	110	100	90	mA	$\overline{RAS}$, $\overline{CAS}$ cycling; t_{RC} = t_{RC} (min); I_O = 0 mA
4217/42S17		140	130	120	110	mA	
4218/42S18		190	180	170	160	mA	
Refresh current ($\overline{RAS}$ only refresh)	I_{CC3}						
4216/42S16		120	110	100	90	mA	$\overline{RAS}$ cycling; $\overline{CAS}$ ≥ V_{IH} (min); t_{RC} = t_{RC} (min); I_O = 0 mA
4217/42S17		140	130	120	110	mA	
4218/42S18		190	180	170	160	mA	
Operating current (Fast-page mode)	I_{CC4}						
4216/42S16		100	90	80	70	mA	$\overline{CAS}$ cycling; $\overline{RAS}$ ≤ V_{IL} (max); t_{PC} = t_{PC} (min); I_O = 0 mA
4217/42S17		100	90	80	70	mA	
4218/42S18		100	90	80	70	mA	
Refresh current ($\overline{CAS}$ before $\overline{RAS}$ refresh)	I_{CC5}						
4216/42S16		120	110	100	90	mA	$\overline{RAS}$ cycling; t_{RC} = t_{RC} (min); I_O = 0 mA
4217/42S17		140	130	120	110	mA	
4218/42S18		190	180	170	160	mA	
Battery backup current (Standby with $\overline{CAS}$ before $\overline{RAS}$ refresh)	I_{CC6}	t_{RAS} ≤ 300 ns		t_{RAS} ≤ 1 μs			Standby: $\overline{RAS}$ ≥ V_{CC} – 0.2 V; $\overline{RAS}$, $\overline{CAS}$: 0 V ≤ V_{IL} ≤ 0.2 V, V_{CC} – 0.2 V ≤ V_{IH} ≤ V_{IH} (max); $\overline{WE}$, $\overline{OE}$: V_{IH}; Address: don't care; Output: open
42S16		350		500		μA	$\overline{CAS}$ before $\overline{RAS}$ refresh: 4096 cycles, 256 ms
42S17		300		400		μA	$\overline{CAS}$ before $\overline{RAS}$ refresh: 2048 cycles, 256 ms
42S18		250		300		μA	$\overline{CAS}$ before $\overline{RAS}$ refresh: 1024 cycles, 256 ms

DC Current Requirements; 3.3-Volt Devices

Parameter	Symbol	-A60	-A70	-A80	Unit	Test Conditions
Operating current	I_{CC1}					
4216/42S16		100	90	80	mA	$\overline{RAS}$, $\overline{CAS}$ cycling; $t_{RC} = t_{RC}$ (min); I_O = 0 mA
4217/42S17		120	110	100	mA	
4218/42S18		170	160	150	mA	
Refresh current ($\overline{RAS}$ only refresh)	I_{CC3}					
4216/42S16		100	90	80	mA	$\overline{RAS}$ cycling; $\overline{CAS} \geq V_{IH}$ (min); $t_{RC} = t_{RC}$ (min); I_O = 0 mA
4217/42S17		120	110	100	mA	
4218/42S18		170	160	150	mA	
Operating current (Fast-page mode)	I_{CC4}					
4216/42S16		80	70	60	mA	$\overline{CAS}$ cycling; $\overline{RAS} \leq V_{IL}$ (max); $t_{PC} = t_{PC}$ (min); I_O = 0 mA
4217/42S17		80	70	60	mA	
4218/42S18		80	70	60	mA	
Refresh current ($\overline{CAS}$ before $\overline{RAS}$ refresh)	I_{CC5}					
4216/42S16		100	90	80	mA	$\overline{RAS}$ cycling; $t_{RC} = t_{RC}$ (min); I_O = 0 mA
4217/42S17		120	110	100	mA	
4218/42S18		170	160	150	mA	
Battery backup current (Standby with $\overline{CAS}$ before $\overline{RAS}$ refresh)	I_{CC6}	$t_{RAS} \leq$ 300 ns		$t_{RAS} \leq$ 1 μs		Standby: $\overline{RAS} \geq V_{CC} - 0.2$ V; $\overline{RAS}$, $\overline{CAS}$: 0 V ≤ $V_{IL} \leq$ 0.2 V, $V_{CC} - 0.2$ V ≤ $V_{IH} \leq V_{IH}$ (max); $\overline{WE}$, $\overline{OE}$: V_{IH}; Address: don't care; Output: open
42S16		140		140	μA	$\overline{CAS}$ before $\overline{RAS}$ refresh: 4096 cycles, 256 ms
42S17		120		120	μA	$\overline{CAS}$ before $\overline{RAS}$ refresh: 2048 cycles, 256 ms
42S18		110		110	μA	$\overline{CAS}$ before $\overline{RAS}$ refresh: 1024 cycles, 256 ms

AC Characteristics

T_A = 0 to +70°C; V_{CC} = +5.0 V ±10% (-50, -60, -70, -80) or +3.3 V ±0.3 V (-A60, -A70, -A80)

		-50		-60, -A60		-70, -A70		-80, -A80			
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**
Access time from column address	t_{AA}		25		30		35		40	ns	(Notes 7, 8)
Access time from $\overline{CAS}$ precharge (rising edge)	t_{ACP}		30		35		40		45	ns	(Note 7)
Column address setup time	t_{ASC}	0		0		0		0		ns	
Row address setup time	t_{ASR}	0		0		0		0		ns	
Column address to $\overline{WE}$ delay time	t_{AWD}	45		53		60		65		ns	(Note 15)
Access time from $\overline{CAS}$ (falling edge)	t_{CAC}		13		15		18		20	ns	(Notes 7, 8)
Column address hold time	t_{CAH}	13		15		15		15		ns	
$\overline{CAS}$ pulse width	t_{CAS}	13	10,000	15	10,000	18	10,000	20	10,000	ns	
$\overline{CAS}$ hold time for $\overline{CAS}$ before $\overline{RAS}$ refresh cycle	t_{CHR}	10		10		10		10		ns	
$\overline{CAS}$ hold time (CBR self-refresh mode)	t_{CHS}	−50		−50		−50		−50		ns	(Note 16)
$\overline{CAS}$ to output in low-Z	t_{CLZ}	0		0		0		0		ns	(Note 7)
Fast-page $\overline{CAS}$ precharge time	t_{CP}	8		10		10		10		ns	
$\overline{CAS}$ precharge time	t_{CPN}	8		10		10		10		ns	
Fast-page $\overline{CAS}$ precharge to $\overline{WE}$ delay time	t_{CPWD}	55		60		65		70		ns	(Note 14)
$\overline{CAS}$ to $\overline{RAS}$ precharge time	t_{CRP}	5		5		5		5		ns	(Note 10)
$\overline{CAS}$ hold time	t_{CSH}	50		60		70		80		ns	
$\overline{CAS}$ setup time for $\overline{CAS}$ before $\overline{RAS}$ refresh cycle	t_{CSR}	5		5		5		5		ns	
$\overline{CAS}$ to $\overline{WE}$ delay	t_{CWD}	33		38		43		45		ns	(Note 15)
Write command referenced to $\overline{CAS}$ lead time	t_{CWL}	13		15		15		15		ns	
Data-in hold time	t_{DH}	10		10		15		15		ns	(Note 13)
Data-in setup time	t_{DS}	0		0		0		0		ns	(Note 13)
Masked write hold time referenced to $\overline{RAS}$	t_{MRH}	0		0		0		0		ns	
Access time from $\overline{OE}$	t_{OEA}		13		15		18		20	ns	(Notes 3, 4, 7, 8)
$\overline{OE}$ data delay time	t_{OED}	10		13		15		15		ns	
$\overline{OE}$ command hold time	t_{OEH}	0		0		0		0		ns	
$\overline{OE}$ to $\overline{RAS}$ inactive setup time	t_{OES}	0		0		0		0		ns	
Output turnoff delay from $\overline{OE}$	t_{OEZ}	0	10	0	13	0	15	0	15	ns	(Note 9)

AC Characteristics (cont)

Parameter	Symbol	-50 Min	-50 Max	-60, -A60 Min	-60, -A60 Max	-70, -A70 Min	-70, -A70 Max	-80, -A80 Min	-80, -A80 Max	Unit	Test Conditions
Output disable from $\overline{CAS}$ high	t_{OFF}	0	10	0	13	0	15	0	15	ns	(Note 9)
$\overline{OE}$ to output in low-Z	t_{OLZ}	0		0		0		0		ns	(Note 7)
Fast-page read or write cycle time	t_{PC}	35		40		45		50		ns	(Note 6)
Fast-page read-modify-write cycle time with extended data output	t_{PRWC}	80		85		90		100		ns	(Note 6)
Access time from $\overline{RAS}$	t_{RAC}		50		60		70		80	ns	(Notes 7, 8)
$\overline{RAS}$ to column address delay time	t_{RAD}	13	25	15	30	15	35	17	40	ns	(Note 8)
Row address hold time	t_{RAH}	8		10		10		12		ns	
Column address lead time referenced to $\overline{RAS}$ (rising edge)	t_{RAL}	25		30		35		40		ns	
$\overline{RAS}$ pulse width	t_{RAS}	50	10,000	60	10,000	70	10,000	80	10,000	ns	
Fast-page $\overline{RAS}$ pulse width	t_{RASP}	50	125,000	60	125,000	70	125,000	80	125,000	ns	
$\overline{RAS}$ pulse width (CBR self-refresh mode)	t_{RASS}	100		100		100		100		μs	(Note 16)
Random read or write cycle time	t_{RC}	90		110		130		150		ns	(Note 6)
$\overline{RAS}$ to $\overline{CAS}$ delay time	t_{RCD}	18	32	20	45	20	50	25	60	ns	(Note 8)
Read command hold time referenced to $\overline{CAS}$	t_{RCH}	0		0		0		0		ns	(Note 11)
Read command setup time	t_{RCS}	0		0		0		0		ns	
Refresh period	t_{REF}										
4216			64		64		64		64	ms	
4217			32		32		32		32	ms	
4218			16		16		16		16	ms	
42S16			256		256		256		256	ms	
42S17			256		256		256		256	ms	
42S18			256		256		256		256	ms	
$\overline{RAS}$ hold time referenced to $\overline{CAS}$ precharge	t_{RHCP}	30		35		40		45		ns	
$\overline{RAS}$ precharge time	t_{RP}	30		40		50		60		ns	
$\overline{RAS}$ precharge $\overline{CAS}$ hold time	t_{RPC}	5		5		5		5		ns	
$\overline{RAS}$ precharge time (CBR self-refresh mode)	t_{RPS}	90		110		130		150		ns	(Note 16)
Read command hold time referenced to $\overline{RAS}$	t_{RRH}	0		0		0		0		ns	(Note 11)
$\overline{RAS}$ hold time	t_{RSH}	13		15		18		20		ns	
Read-modify-write cycle time	t_{RWC}	140		160		180		200		ns	(Note 6)

8m

AC Characteristics (cont)

Parameter	Symbol	-50 Min	-50 Max	-60, -A60 Min	-60, -A60 Max	-70, -A70 Min	-70, -A70 Max	-80, -A80 Min	-80, -A80 Max	Unit	Test Conditions
$\overline{RAS}$ to $\overline{WE}$ delay	t_{RWD}	70		83		95		105		ns	(Note 15)
Write command referenced to $\overline{RAS}$ lead time	t_{RWL}	18		20		20		20		ns	
Rise and fall transition time	t_T	3	50	3	50	3	50	3	50	ns	
Write command hold time	t_{WCH}	8		10		10		15		ns	(Note 12)
Write command setup time	t_{WCS}	0		0		0		0		ns	(Note 14)
Write command pulse width	t_{WP}	8		10		10		15		ns	(Note 12)

Notes:

(1) All voltages are referenced to GND.

(2) An initial pause of 100 μs is required after power-up, followed by eight refresh cycles ($\overline{RAS}$ only or CBR) before proper device operation is achieved.

(3) I_{CC1}, I_{CC3}, I_{CC4}, and I_{CC5} depend on output loading and cycle rates. Specified values are obtained with the output open. I_{CC3} is measured assuming that all column address inputs are held at either a high level or a low level during $\overline{RAS}$-only refresh cycles. I_{CC4} is measured assuming that all column address inputs are switched only once during each fast-page cycle.

(4) Ac measurements assume t_T = 5 ns.

(5) V_{IH} (min) and V_{IL} (max) are reference levels for measuring the timing of input signals. Transition times are measured between V_{IH} and V_{IL}.

(6) The minimum specifications are used only to indicate the cycle time at which proper operation over the full temperature range (T_A = 0 to +70 °C) is assured.

(7) Load = 2 TTL (–1 mA, +4 mA) loads and 100 pF.

(8) If $t_{RCD} \leq t_{RCD}$ (max) and $t_{RAD} \leq t_{RAD}$ (max), access time is defined by t_{RAC} (max).
If $t_{RCD} \geq t_{RCD}$ (max), access time is defined by t_{CAC} (max).
If $t_{RAD} \geq t_{RAD}$ (max), access time is defined by t_{AA} (max).

(9) t_{OFF} (max) and t_{OEZ} (max) define the time at which the outputs become open-circuit and are not referenced to V_{OH} or V_{OL}.

(10) The t_{CRP} requirement should be applicable for $\overline{RAS}$/$\overline{CAS}$ cycles preceded by any cycle.

(11) Either t_{RRH} or t_{RCH} must be satisfied for a read cycle.

(12) Parameter t_{WP} is applicable for a late write cycle. For early write cycles, t_{WCH} must be met.

(13) These parameters are referenced to the leading edge of $\overline{CAS}$ in early write cycles and to the leading edge of $\overline{WE}$ in late write or read-modify-write cycles.

(14) If $t_{WCS} \geq t_{WCS}$ (min), the cycle is an early write cycle and the data I/O pins will remain open-circuit throughout the entire cycle.

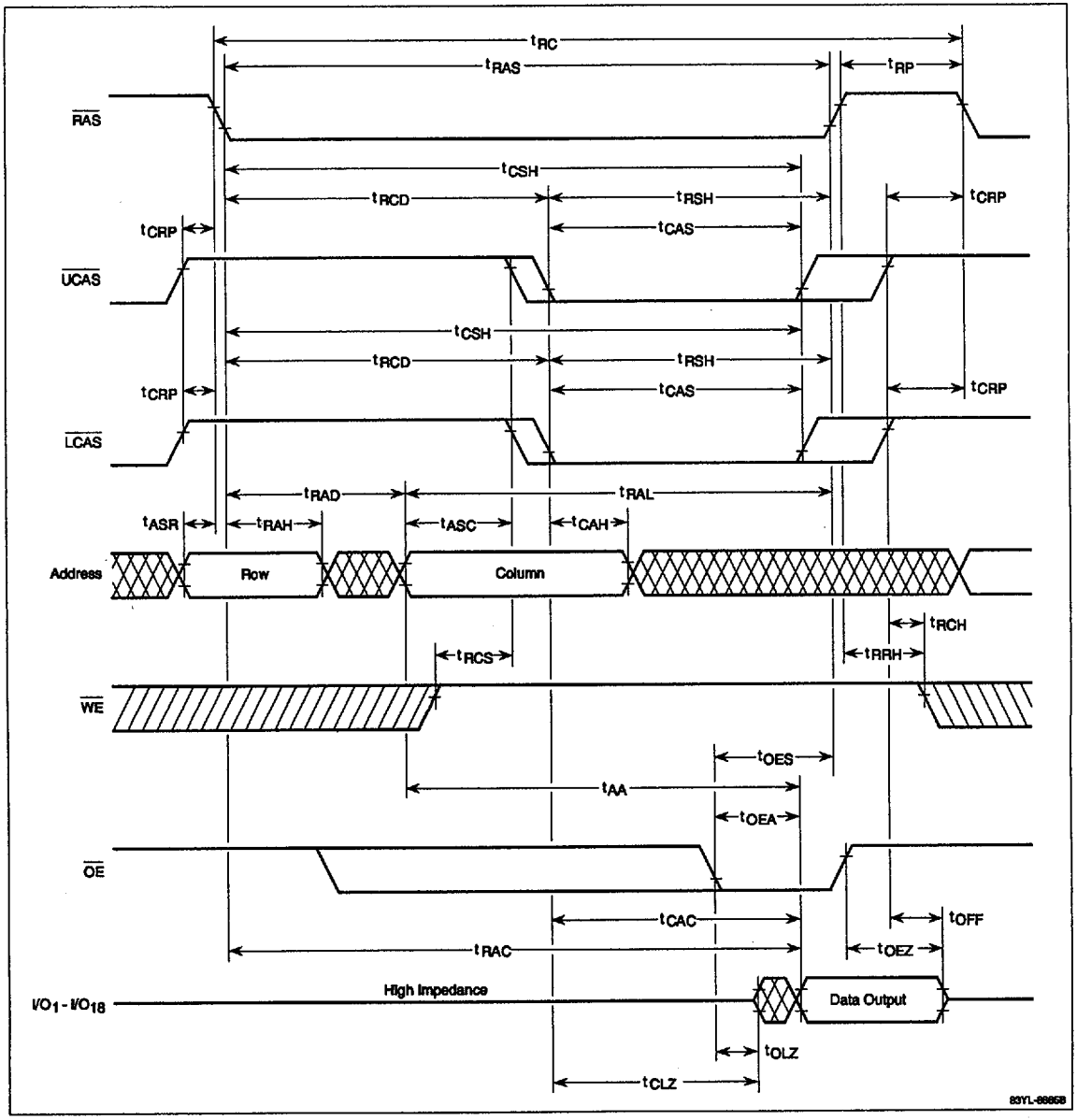
(15) If $t_{CWD} \geq t_{CWD}$ (min), $t_{RWD} \geq t_{RWD}$ (min), and $t_{AWD} \geq t_{AWD}$ (min), then the cycle is a read-write cycle and the data I/O pins will contain data read from the selected cells. If neither of the above conditions is met, the condition of the data I/O pins (at access time and until $\overline{CAS}$ returns to V_{IH}) is indeterminate.

(16) Parameter is applicable only to self-refresh versions.

(17) With burst CBR, $\overline{RAS}$ only, or external $\overline{RAS}$/$\overline{CAS}$, all addresses must be refreshed before entering self-refresh mode and after exiting.

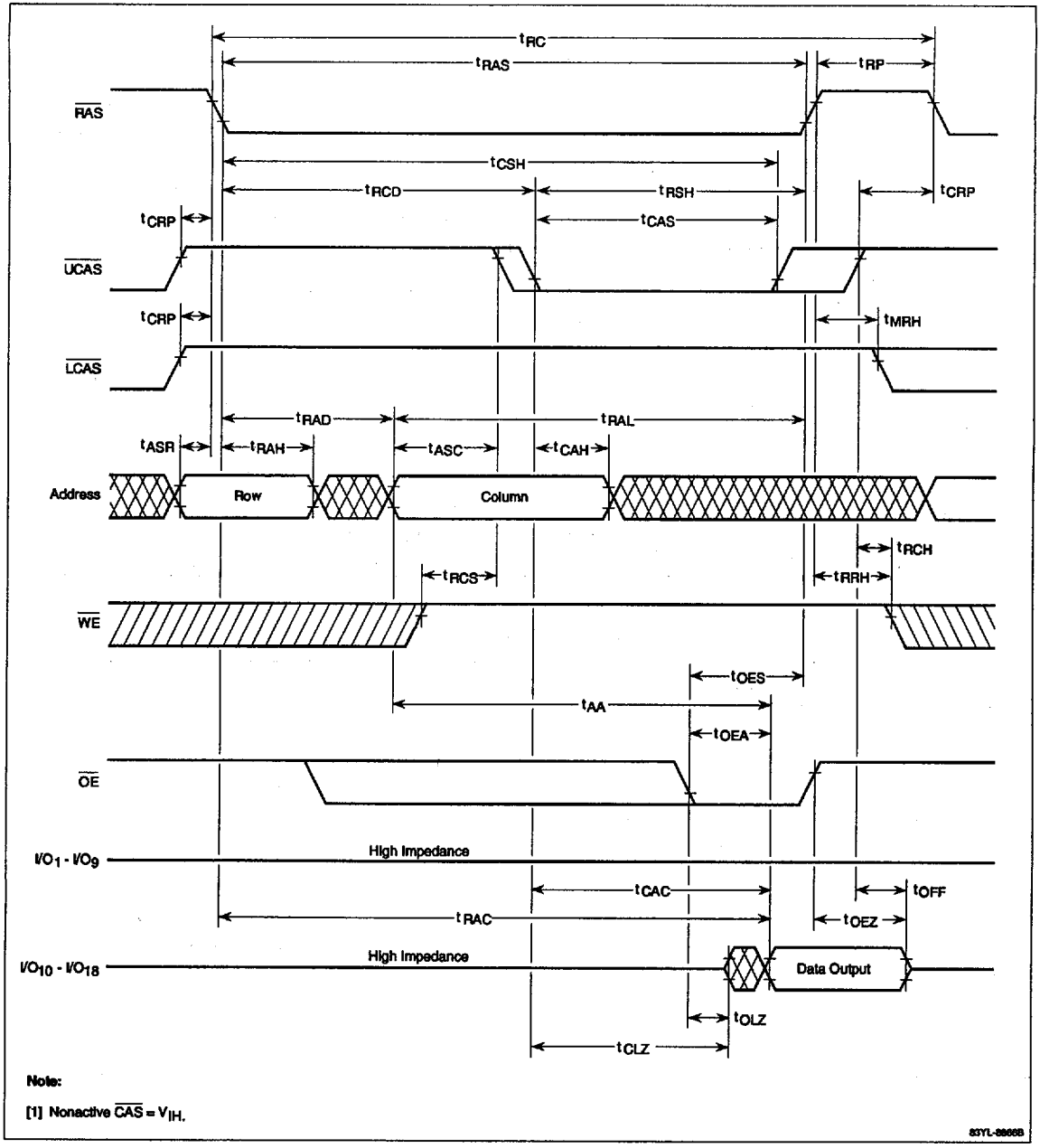
Timing Waveforms

Word Read Cycle



Timing Waveforms (cont)

Byte Read Cycle

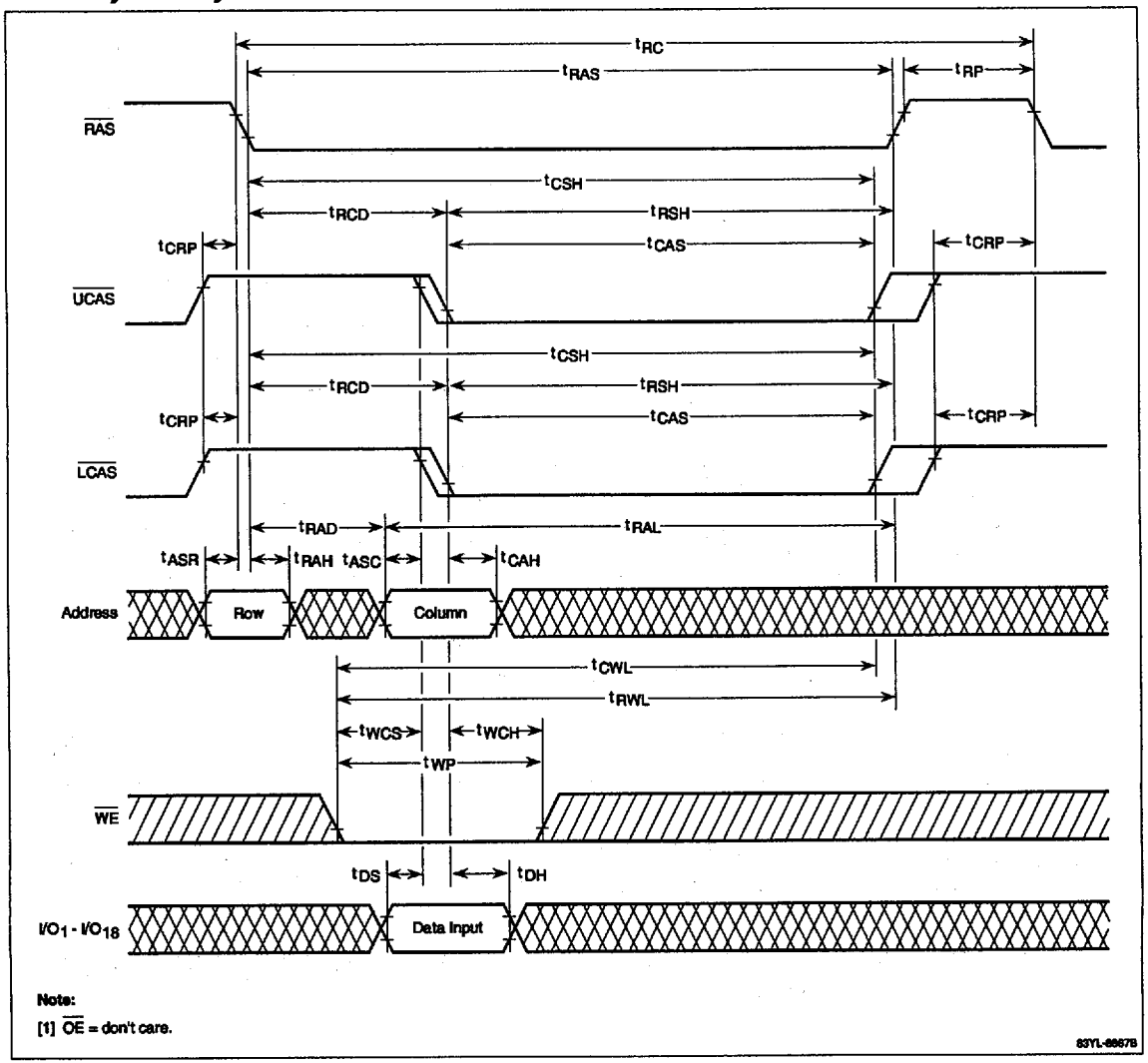


Note:

[1] Nonactive $\overline{CAS} = V_{IH}$.

Timing Waveforms (cont)

Word Early-Write Cycle



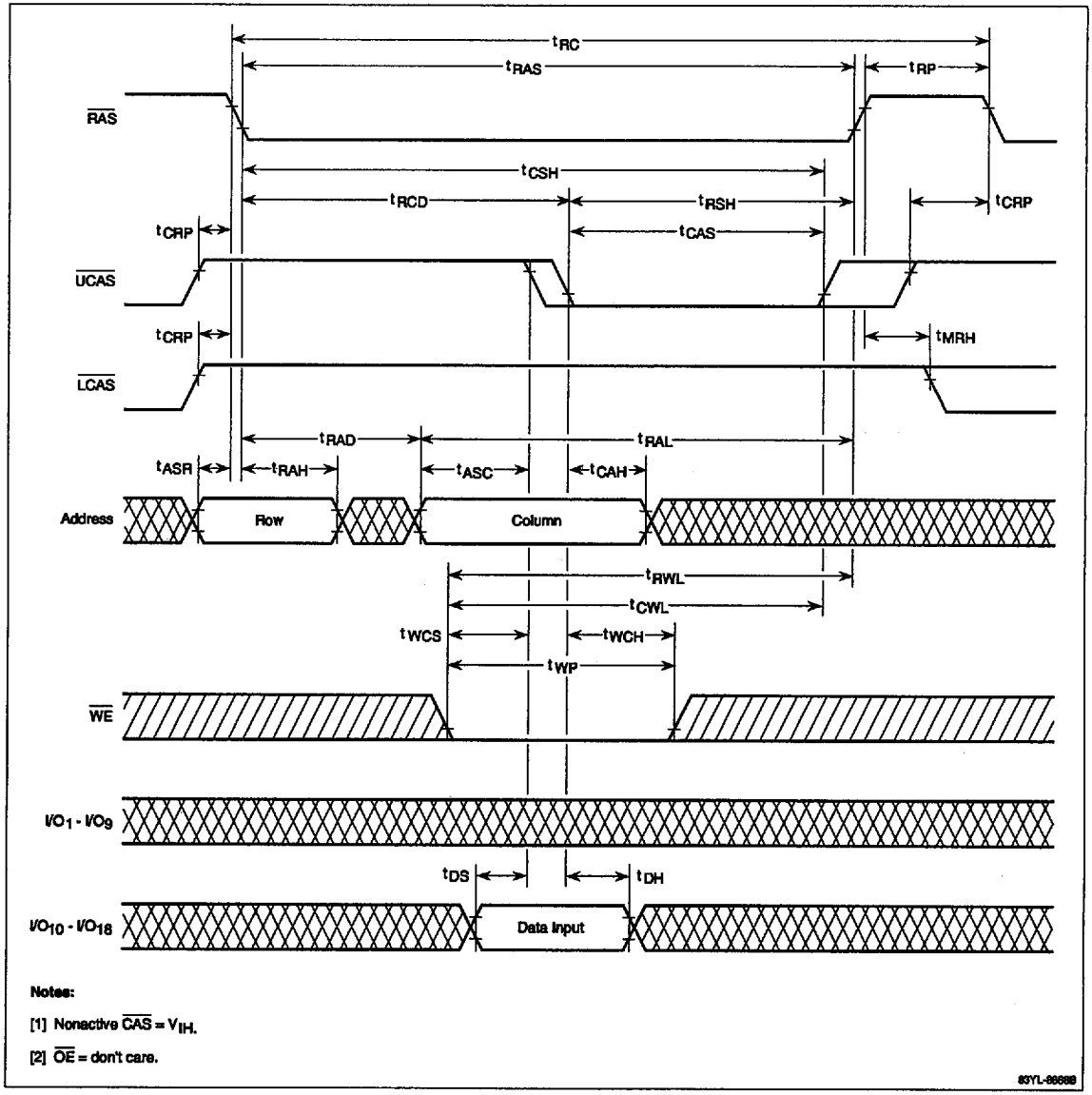
Note:
[1] $\overline{OE}$ = don't care.

83YL-6667B

8m

Timing Waveforms (cont)

Byte Early-Write Cycle



Notes:

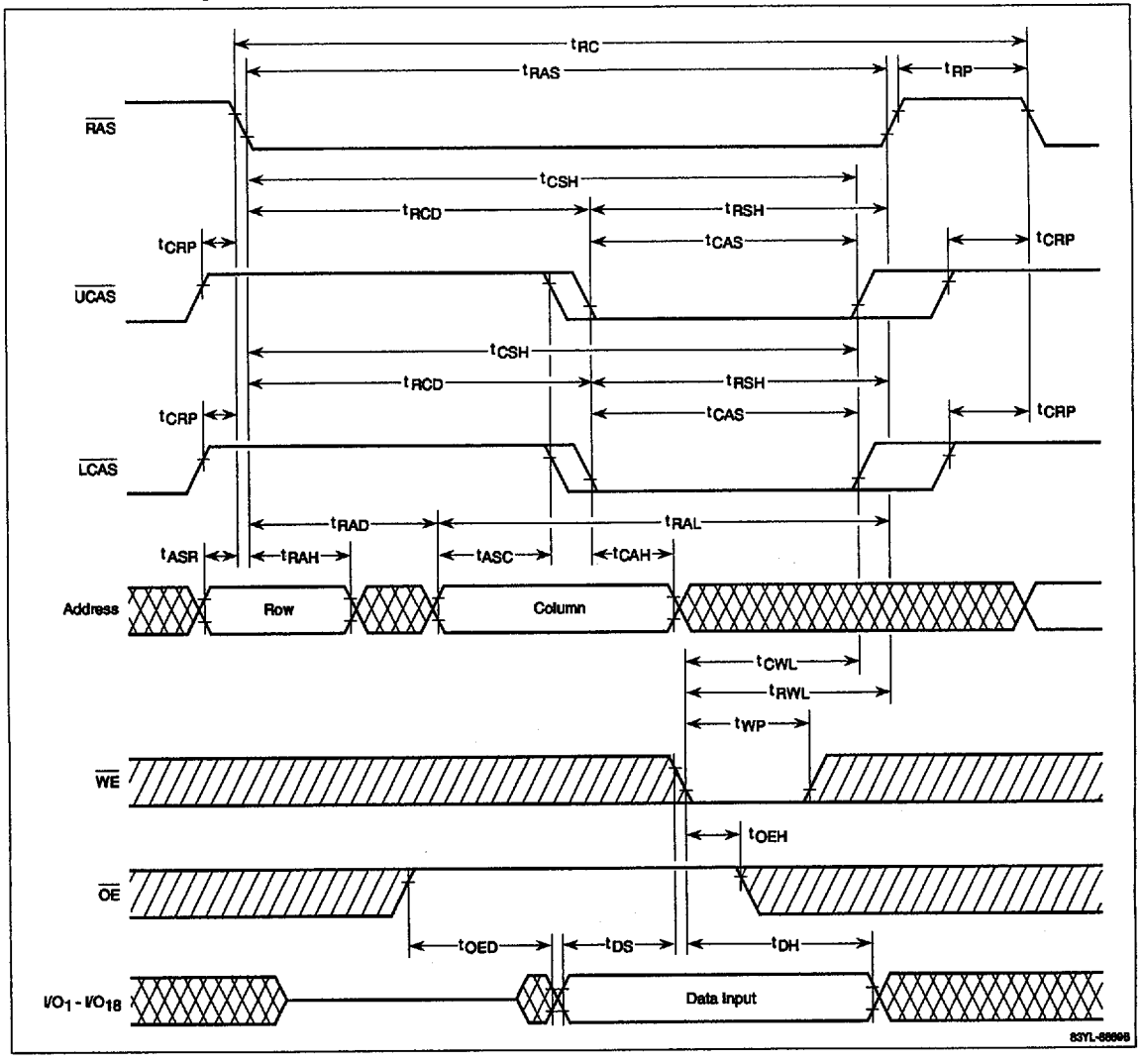
[1] Nonactive $\overline{CAS} = V_{IH}$.

[2] $\overline{OE}$ = don't care.

83YL-86688

Timing Waveforms (cont)

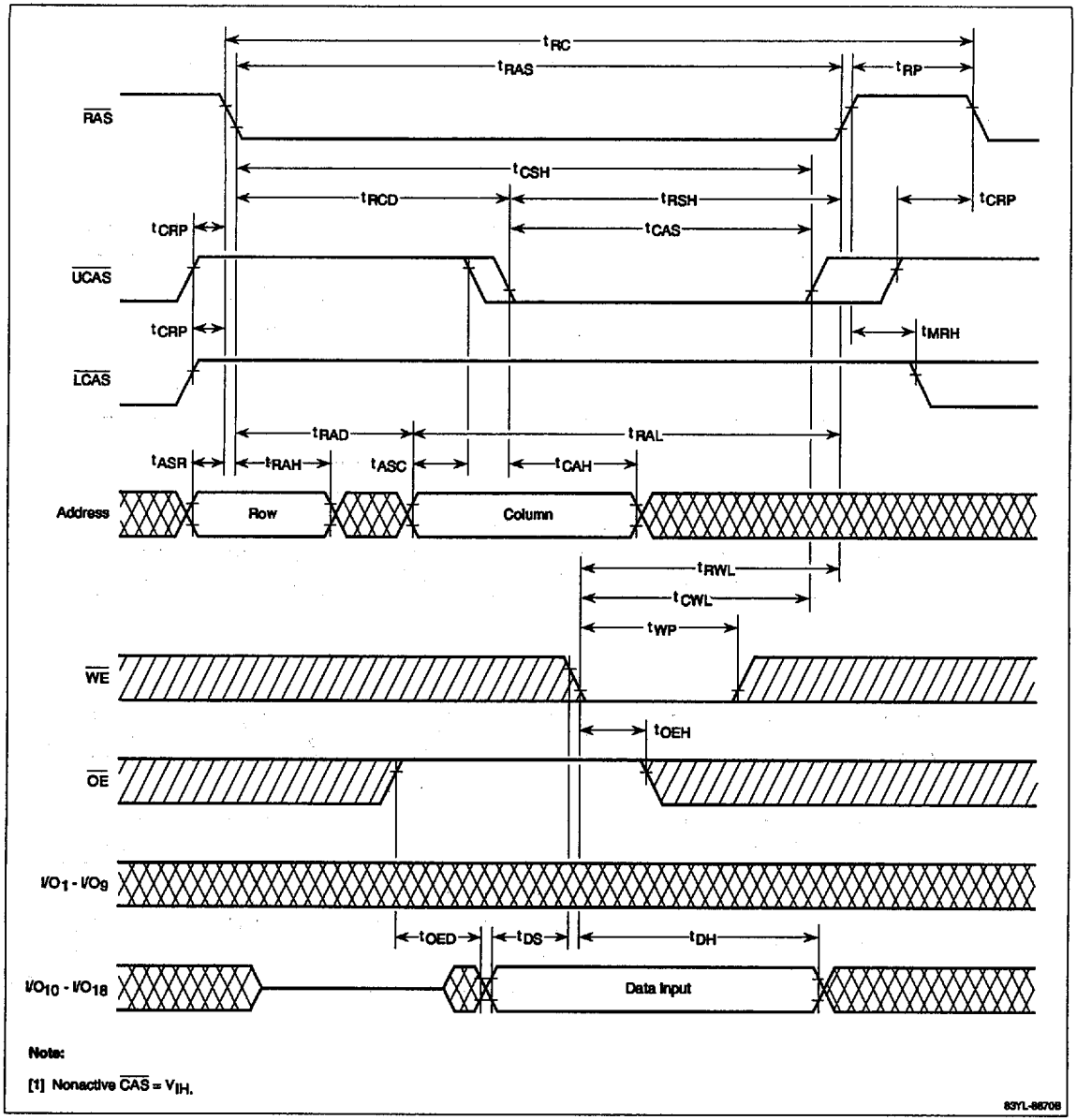
Word Late-Write Cycle



8m

Timing Waveforms (cont)

Byte Late-Write Cycle



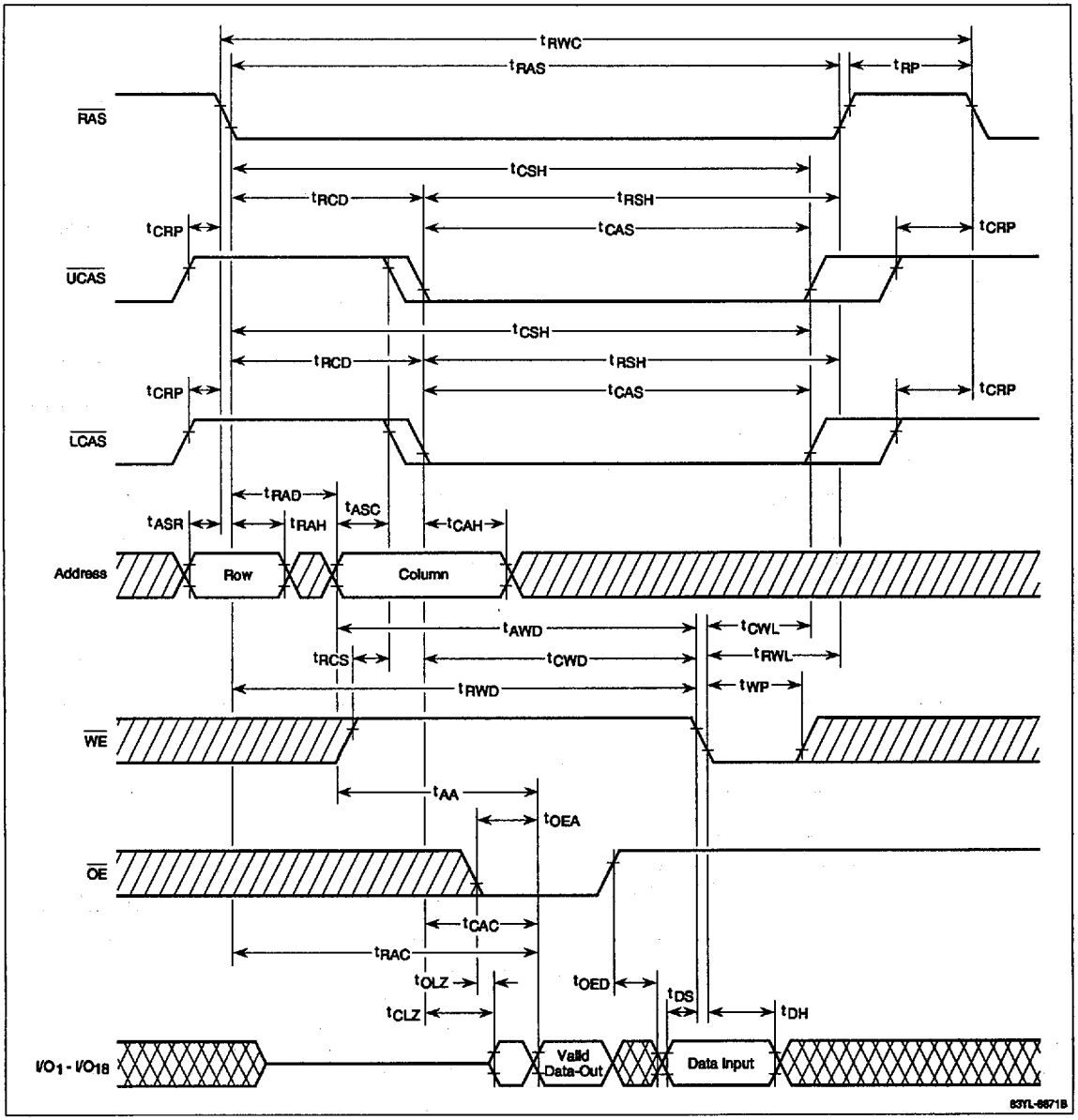
Note:

[1] Nonactive $\overline{CAS} = V_{IH}$.

83YL-86708

Timing Waveforms (cont)

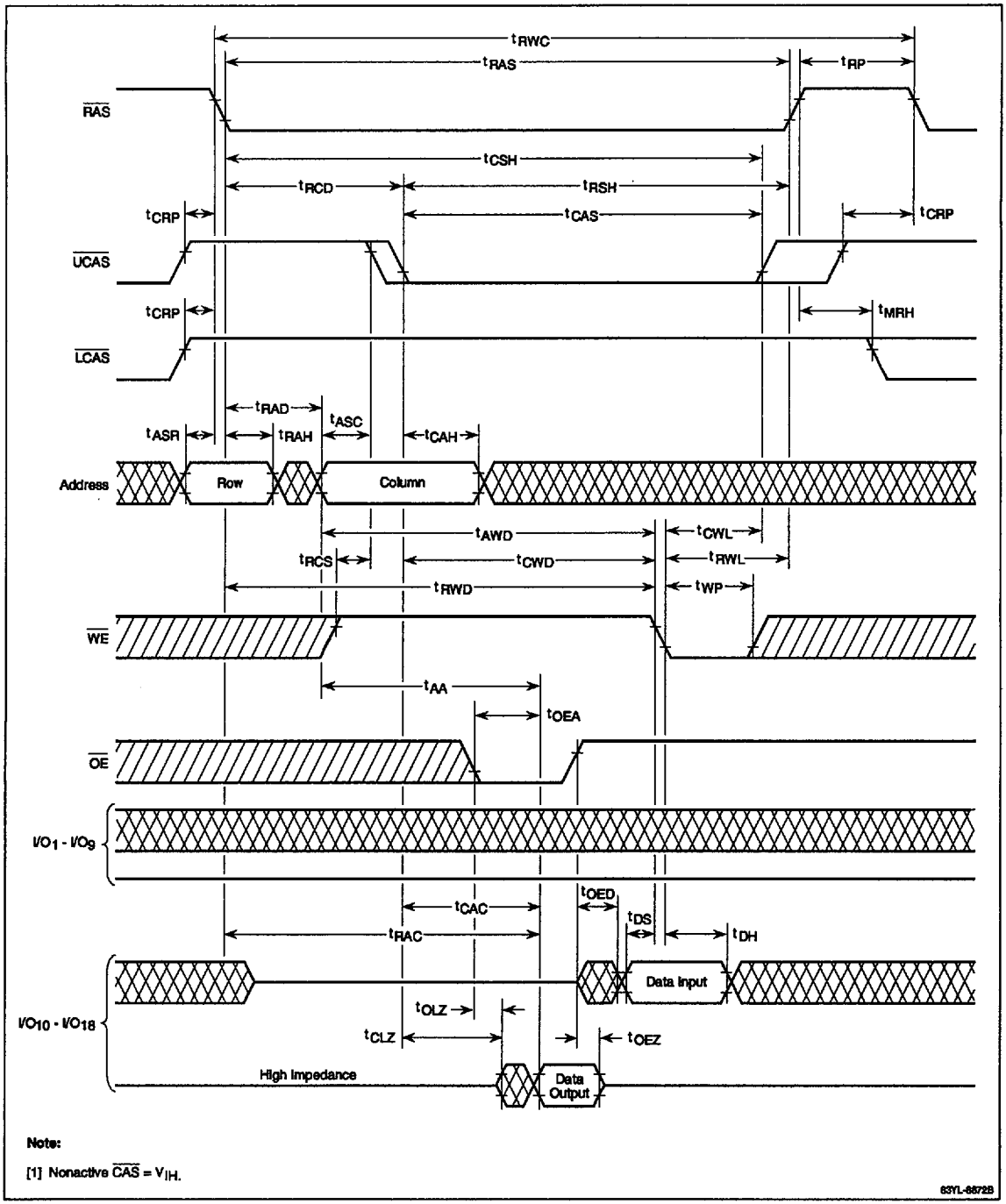
Word Read-Modify-Write Cycle



8m

Timing Waveforms (cont)

Byte Read-Modify-Write Cycle



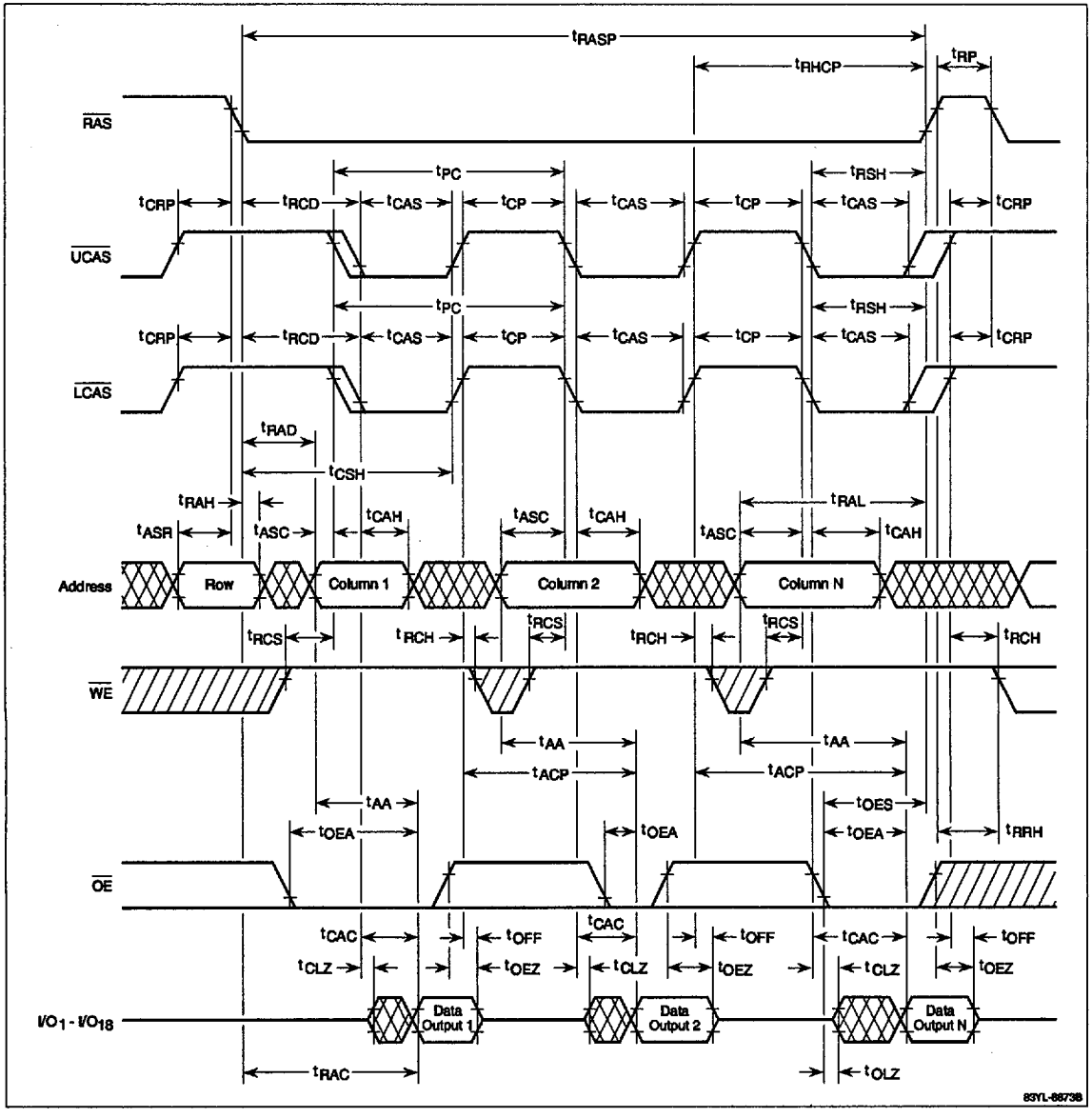
Note:

[1] Nonactive $\overline{CAS} = V_{IH}$.

83YL-6872B

Timing Waveforms (cont)

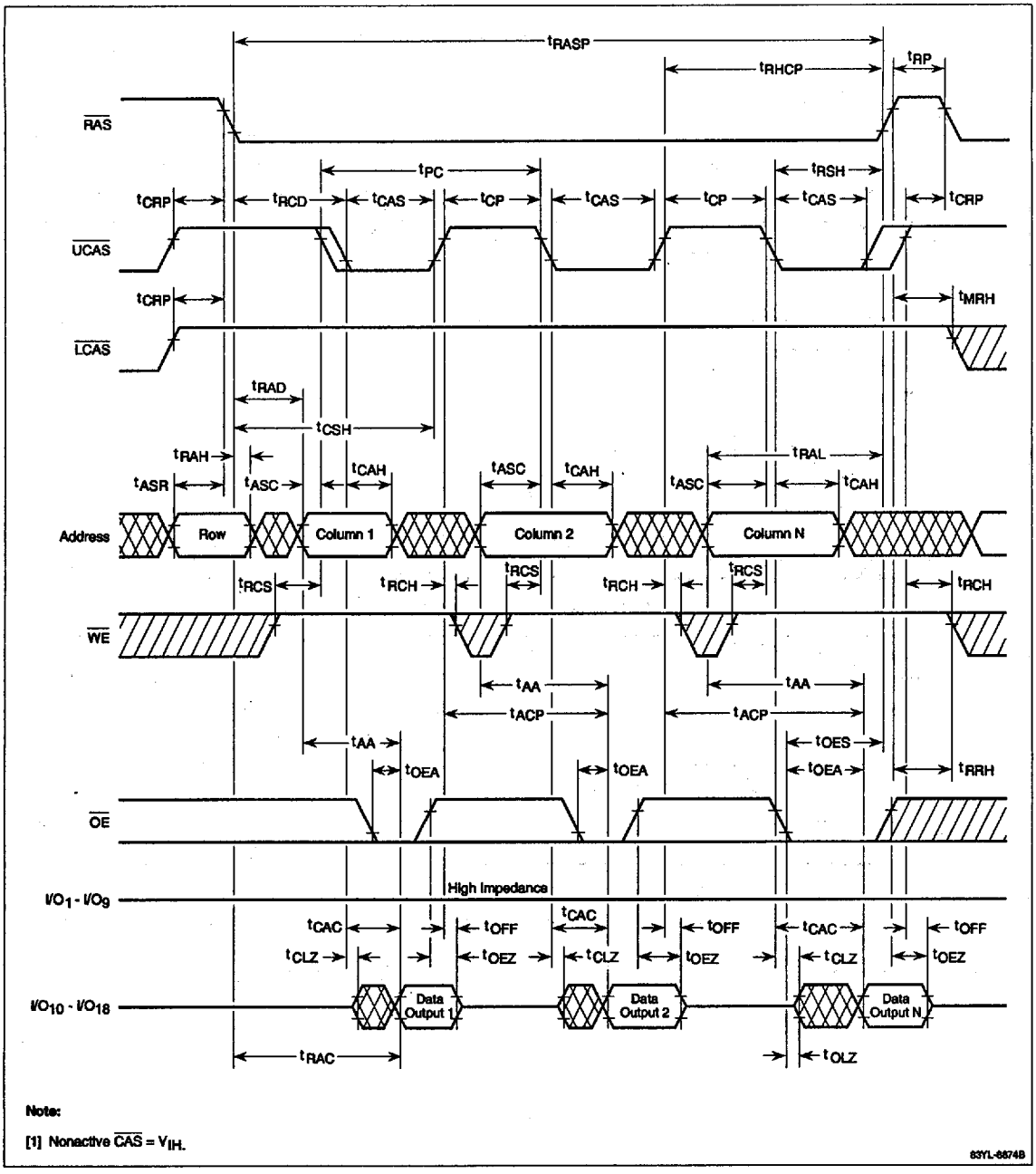
Word Fast-Page Read Cycle



8m

Timing Waveforms (cont)

Byte Fast-Page Read Cycle



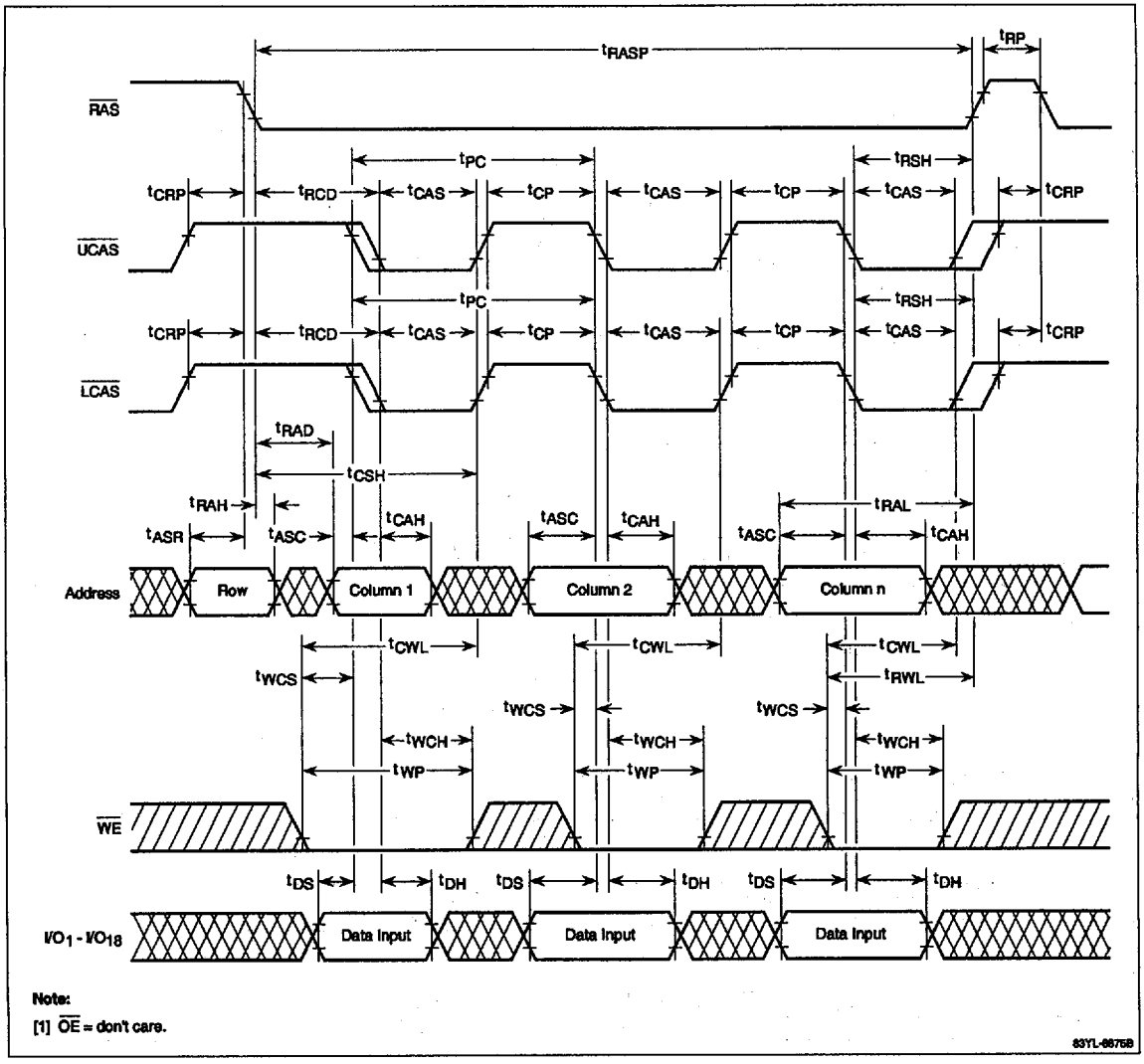
Note:

[1] Nonactive $\overline{CAS}$ = V_{IH}.

83YL-6874B

Timing Waveforms (cont)

Word Fast-Page Early-Write Cycle

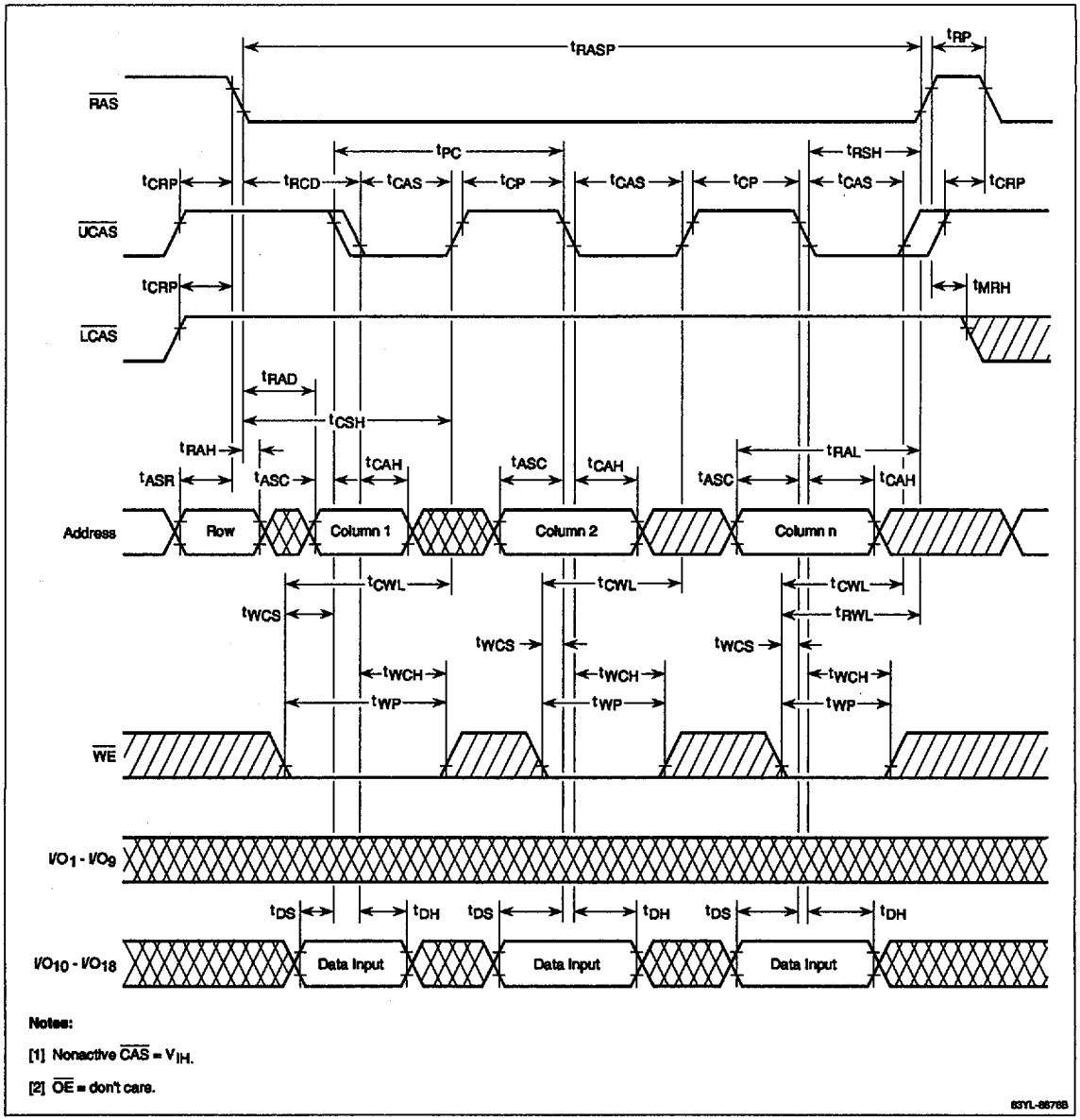


Note:
[1] $\overline{OE}$ = don't care.

83YL-66758

Timing Waveforms (cont)

Byte Fast-Page Early-Write Cycle



Notes:

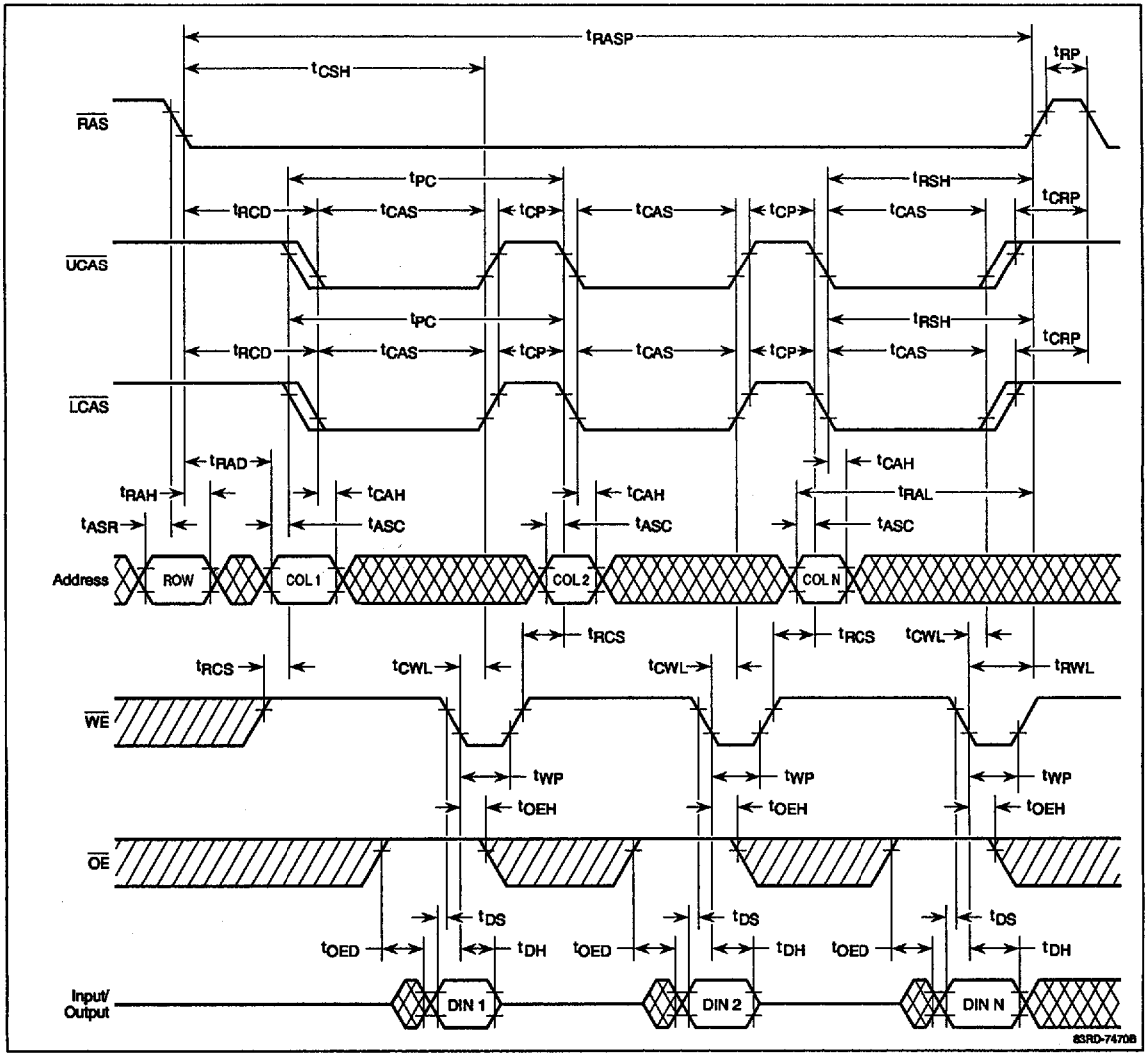
[1] Nonactive $\overline{CAS}$ = V_{IH}.

[2] $\overline{OE}$ = don't care.

83YL-88788

Timing Waveforms (cont)

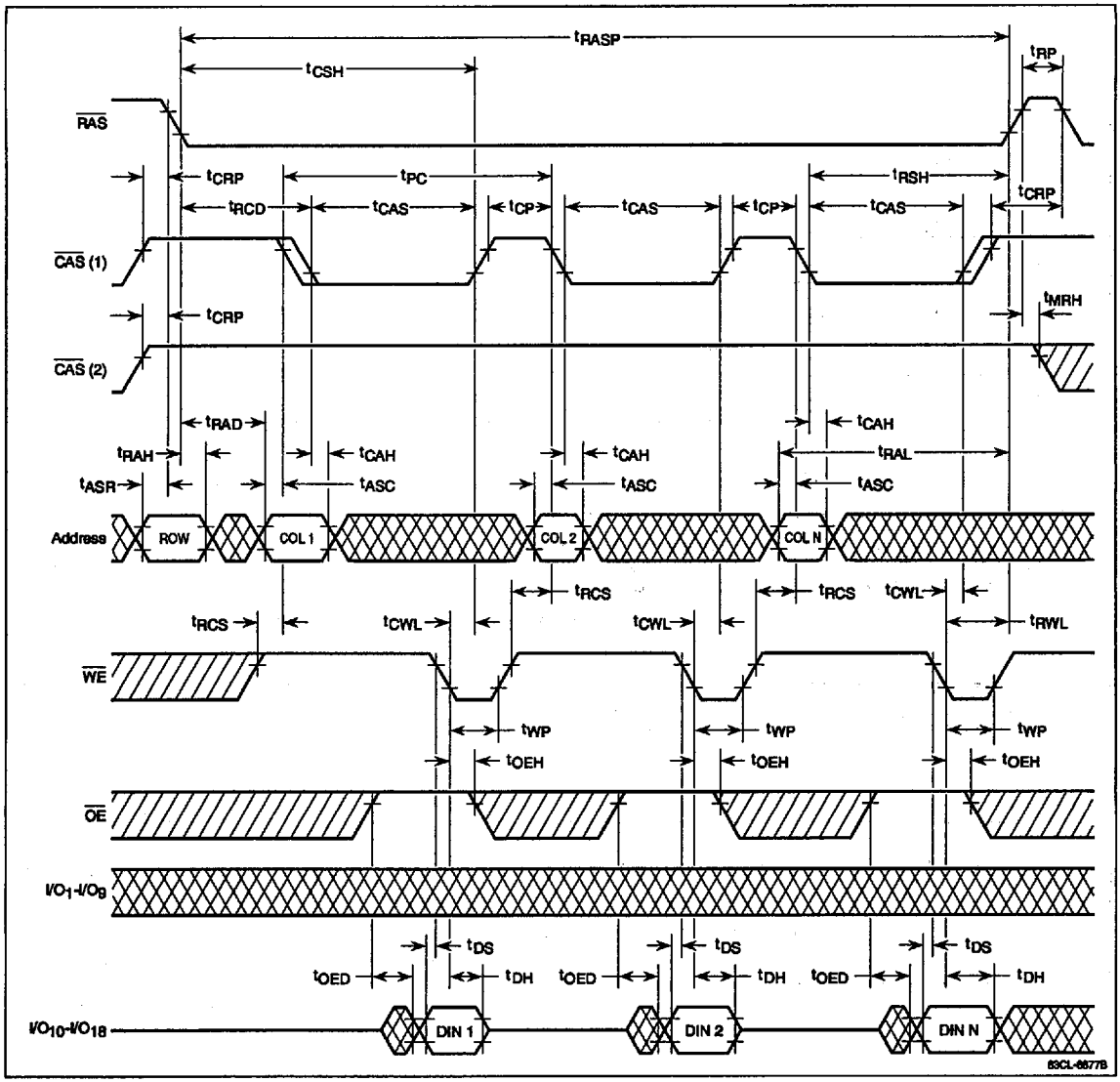
Word Fast-Page Late-Write Cycle



8m

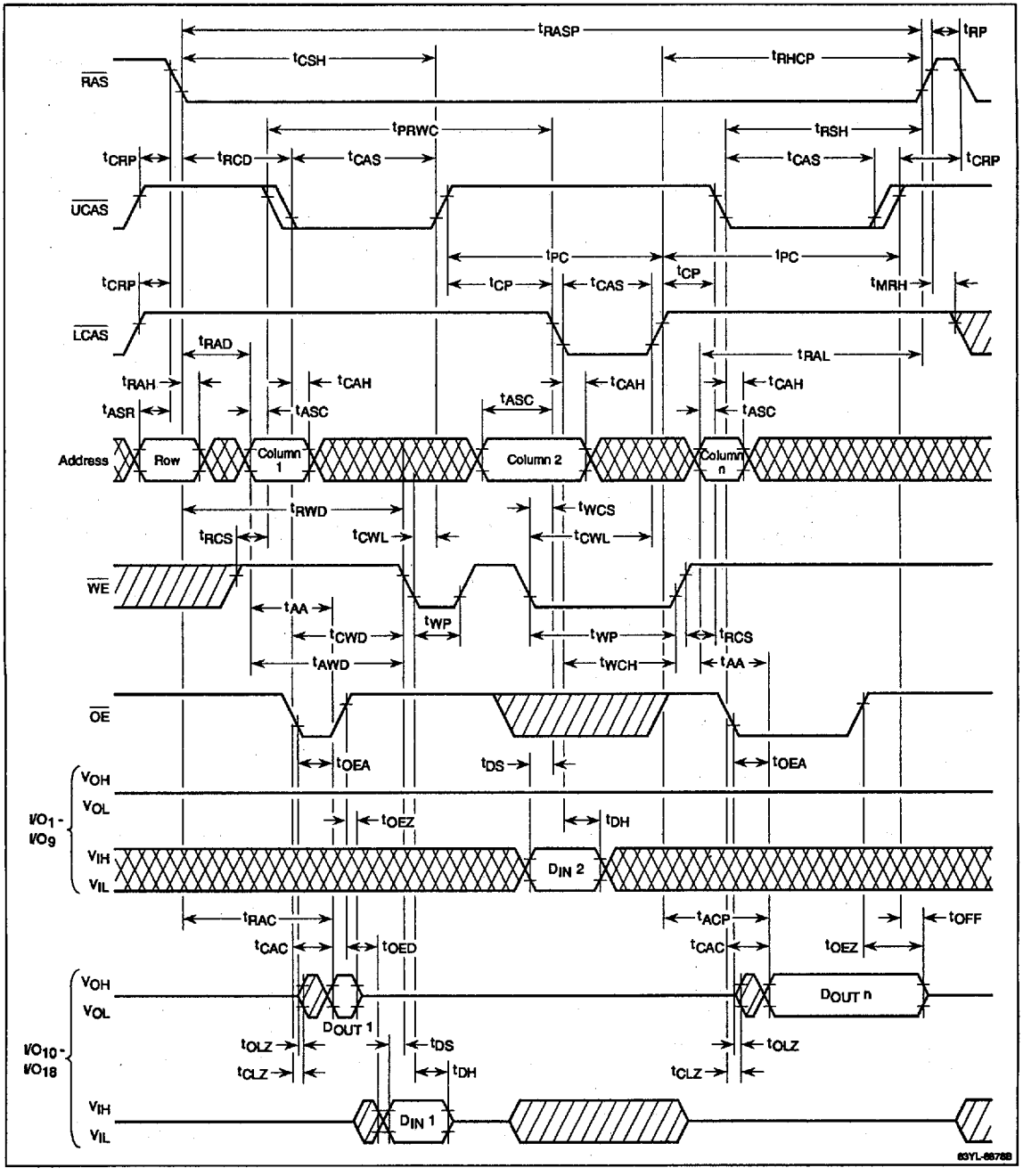
Timing Waveforms (cont)

Byte Fast-Page Late-Write Cycle



Timing Waveforms (cont)

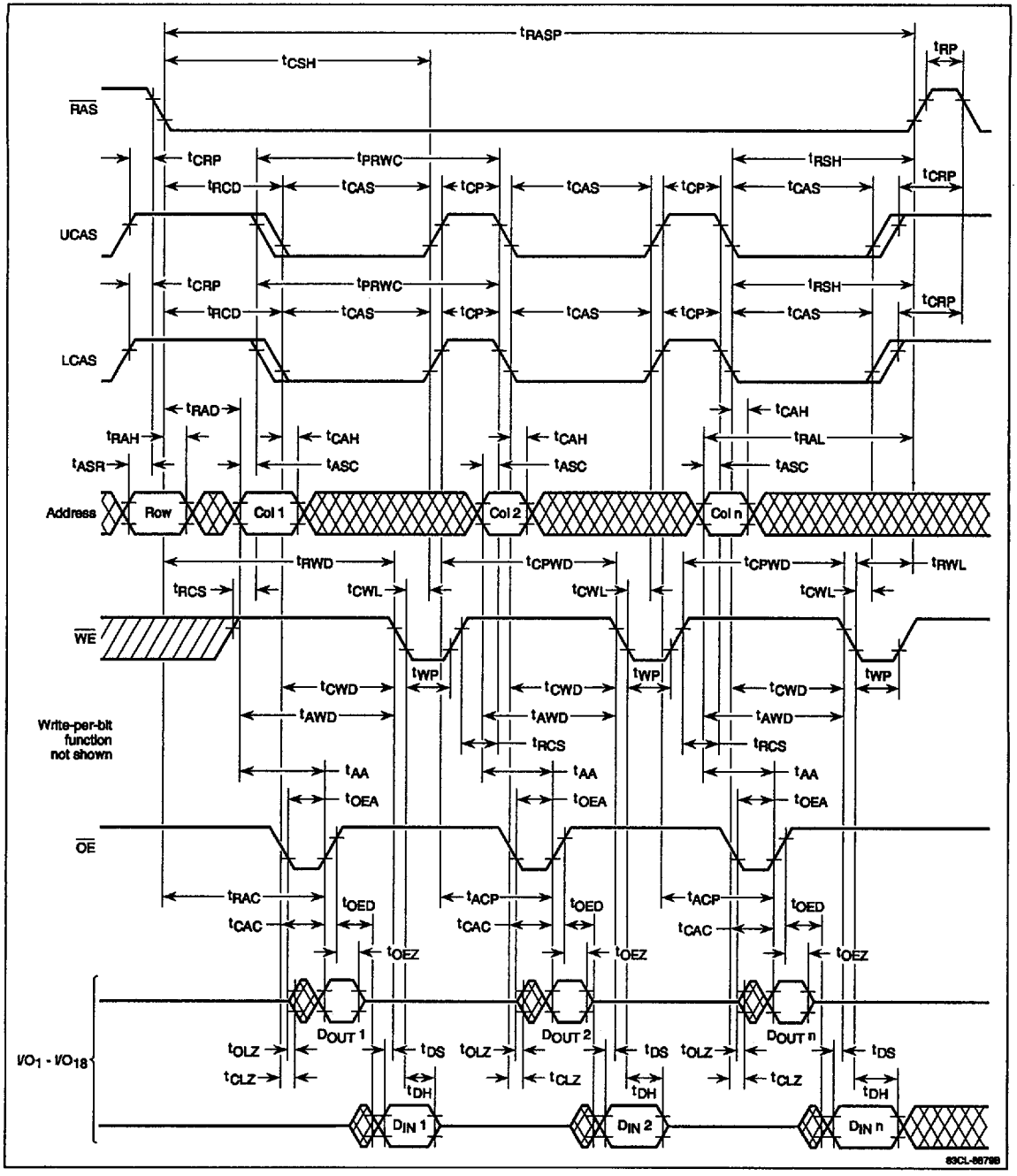
Byte Fast-Page Read/Write Cycle



8m

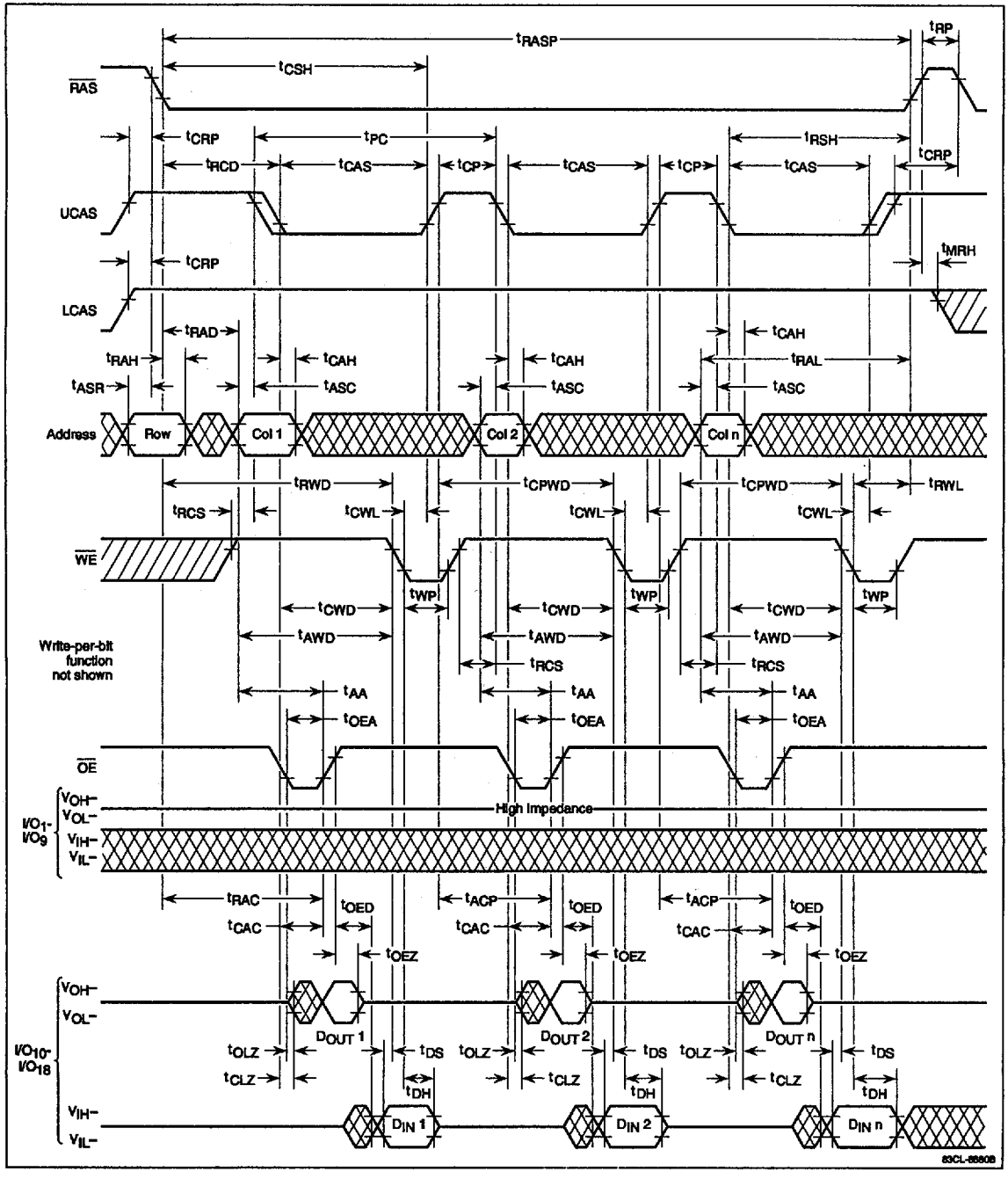
Timing Waveforms (cont)

Word Fast-Page Read-Modify-Write Cycle



Timing Waveforms (cont)

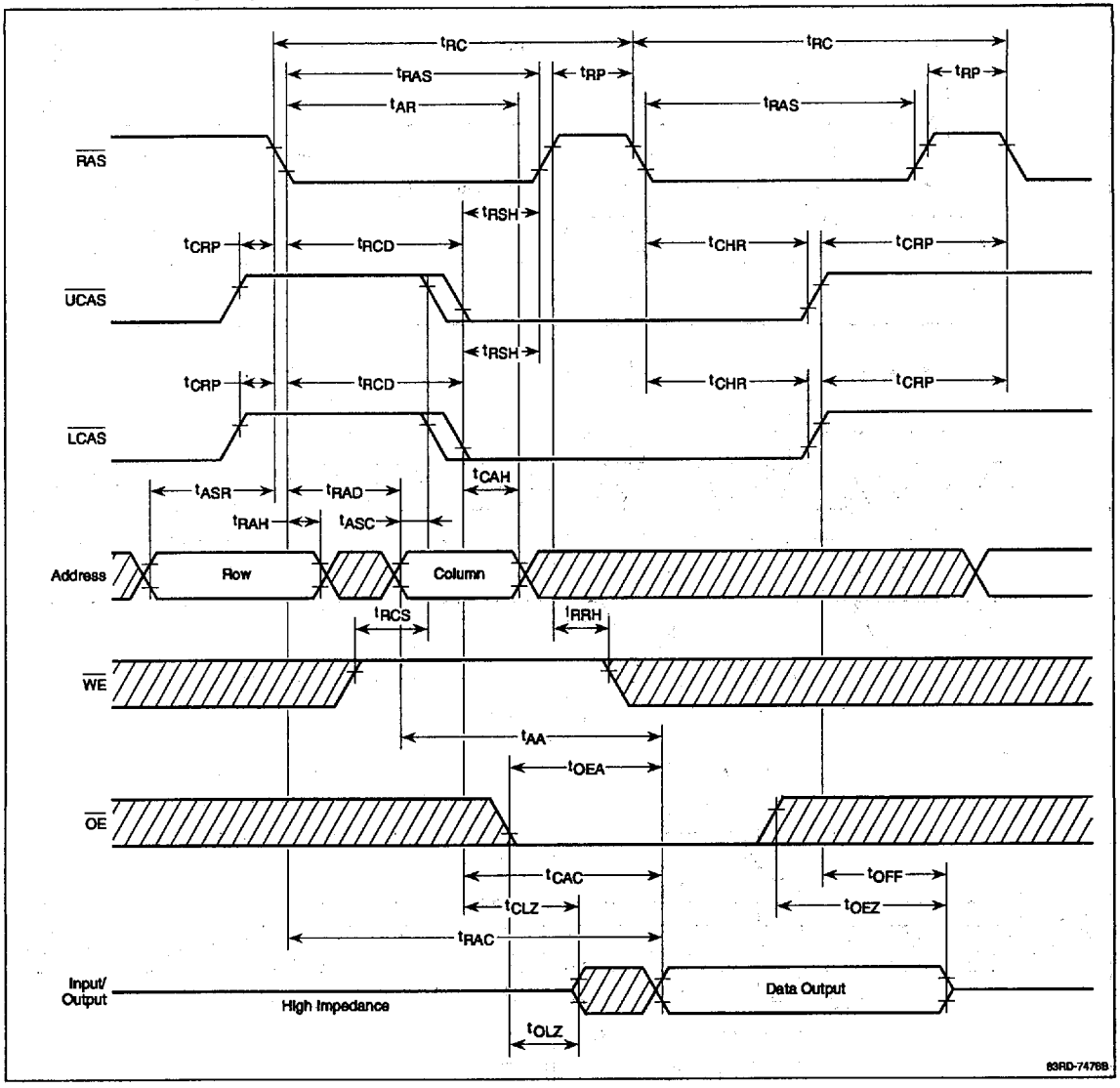
Byte Fast-Page Read-Modify-Write Cycle



8m

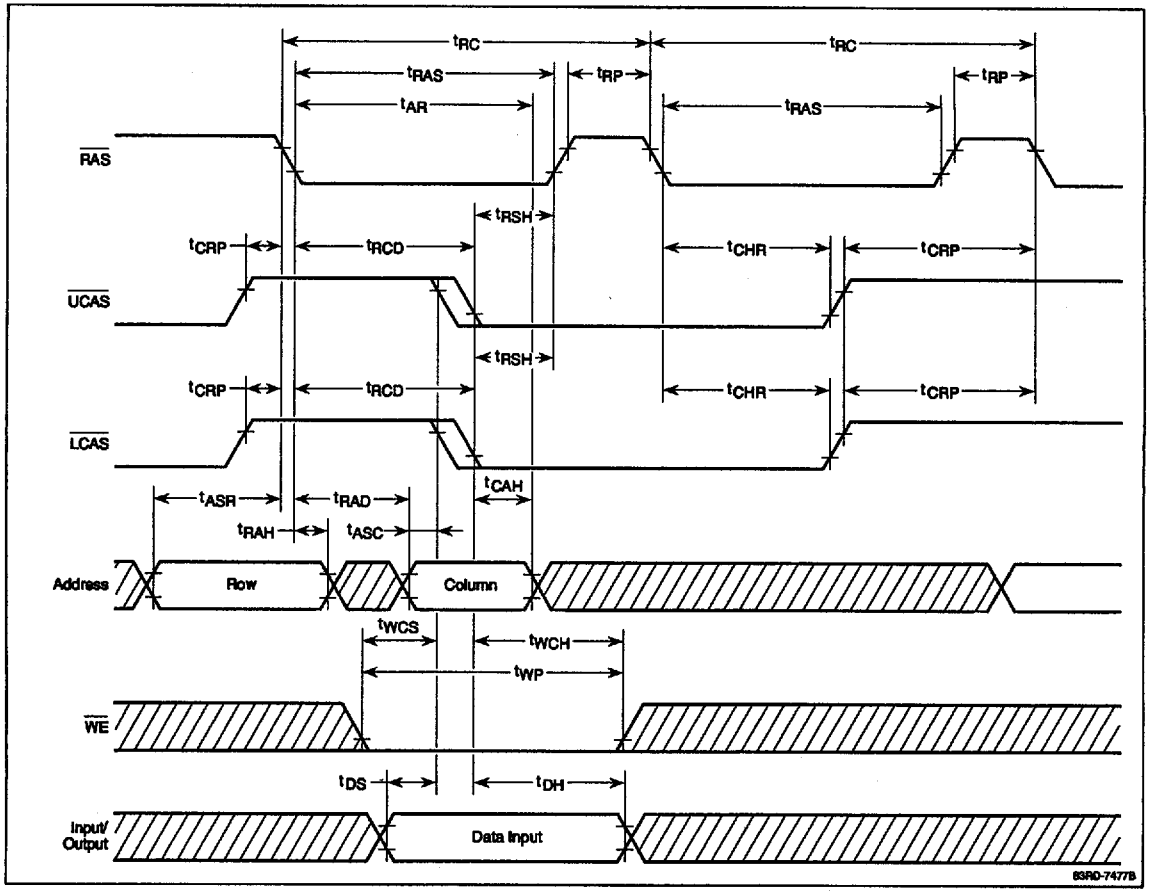
Timing Waveforms (cont)

Hidden-Refresh Cycle (Word Read Cycle)



Timing Waveforms (cont)

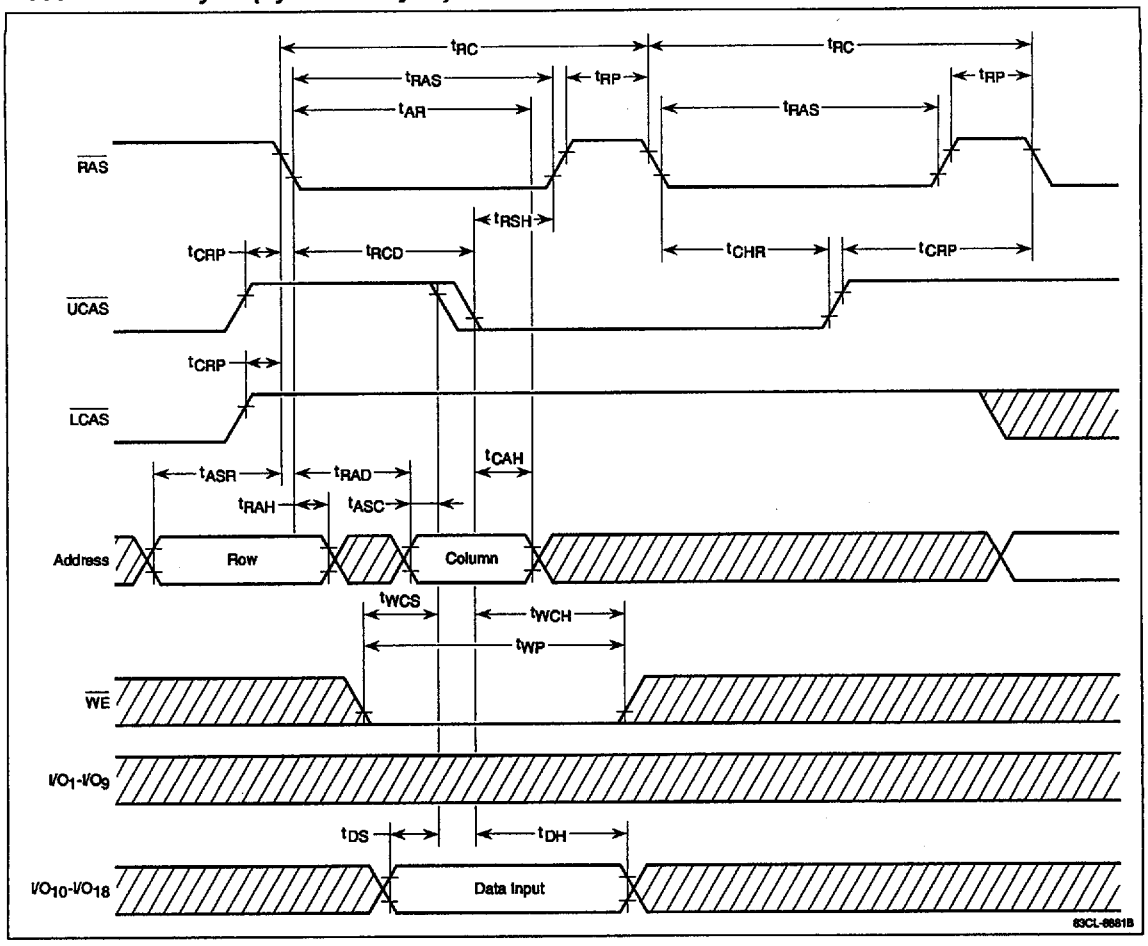
Hidden-Refresh Cycle (Word Write Cycle)



8m

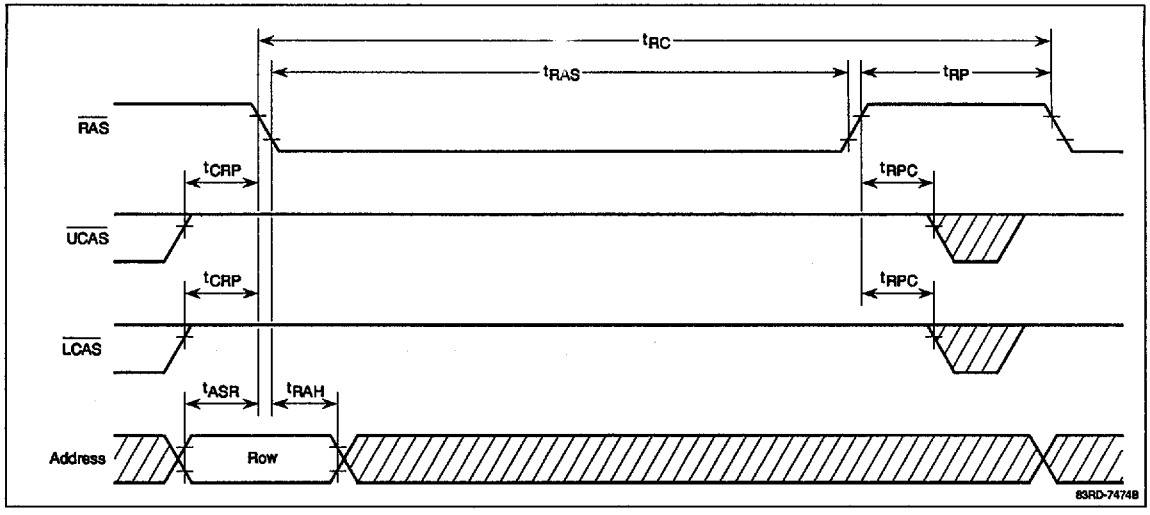
Timing Waveforms (cont)

Hidden-Refresh Cycle (Byte Write Cycle)

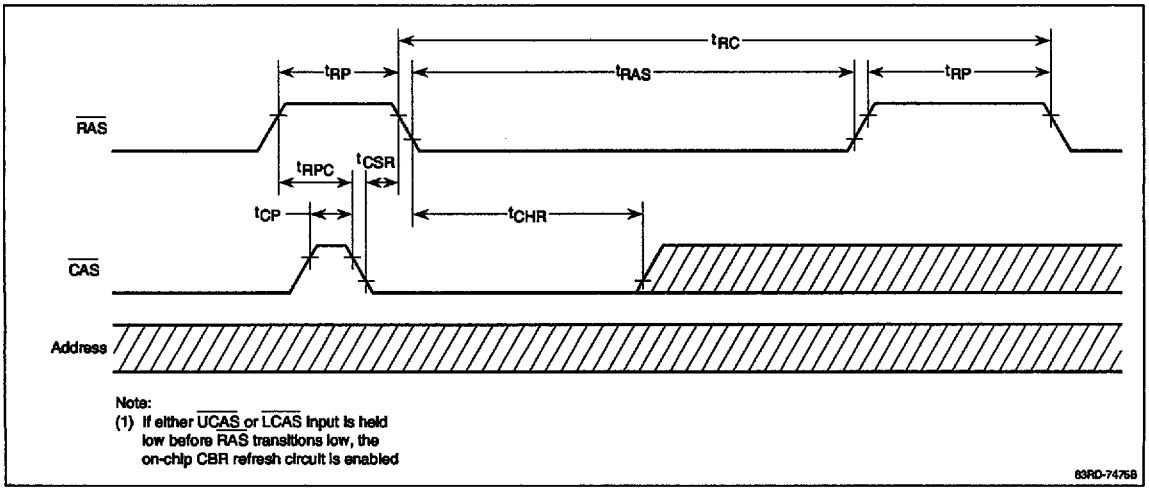


Timing Waveforms (cont)

$\overline{RAS}$-Only Refresh Cycle



$\overline{CAS}$ Before $\overline{RAS}$ Refresh Cycle



8m

Timing Waveforms (cont)

CBR Self-Refresh Cycle